

# Nanostructured Semiconductor Crystals -- Building Blocks for Solar Cells: Shapes, Syntheses, Surface Chemistry, Quantum Confinement Effects

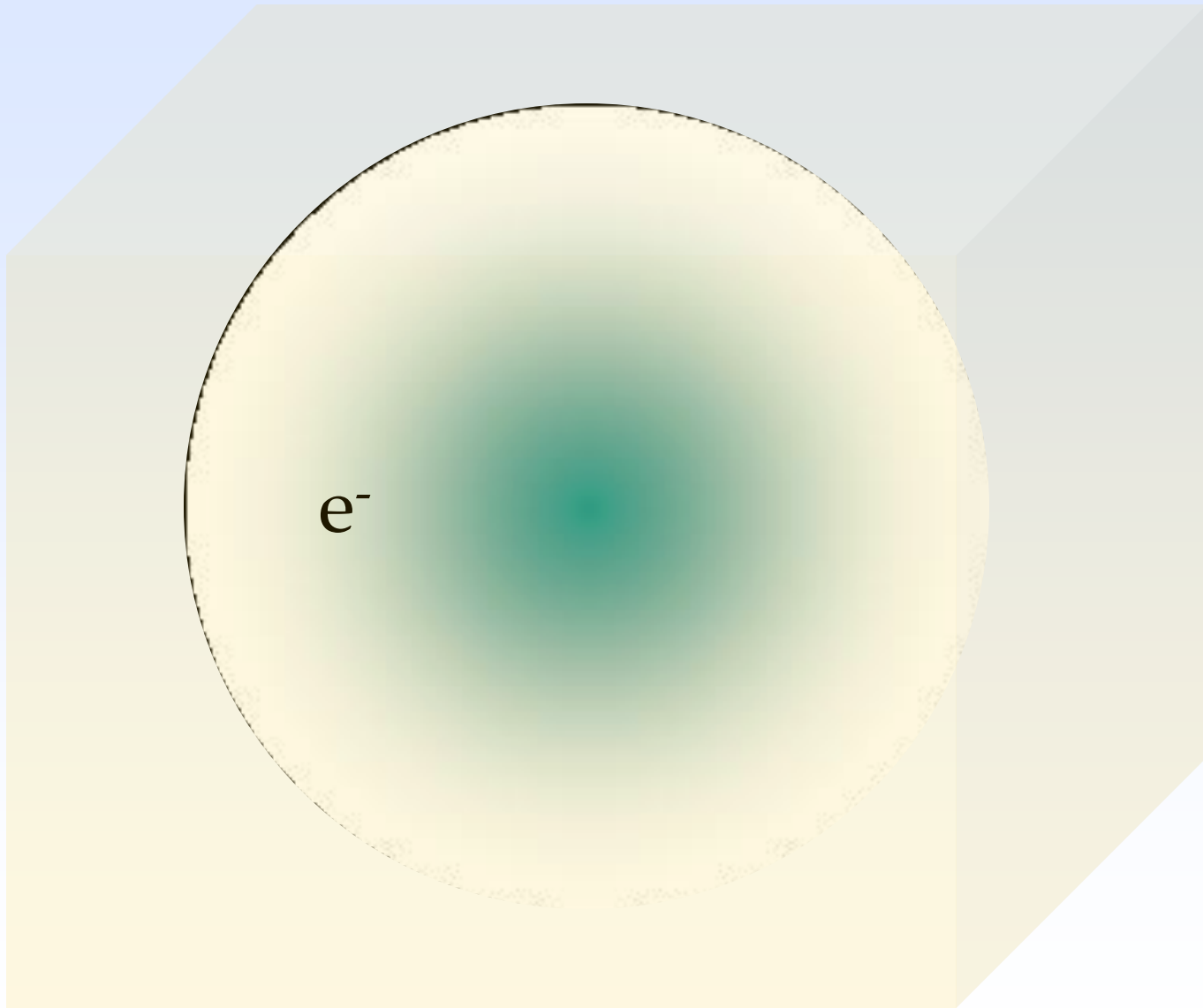
April 14, 2015

The University of Toledo, Department of Physics and Astronomy

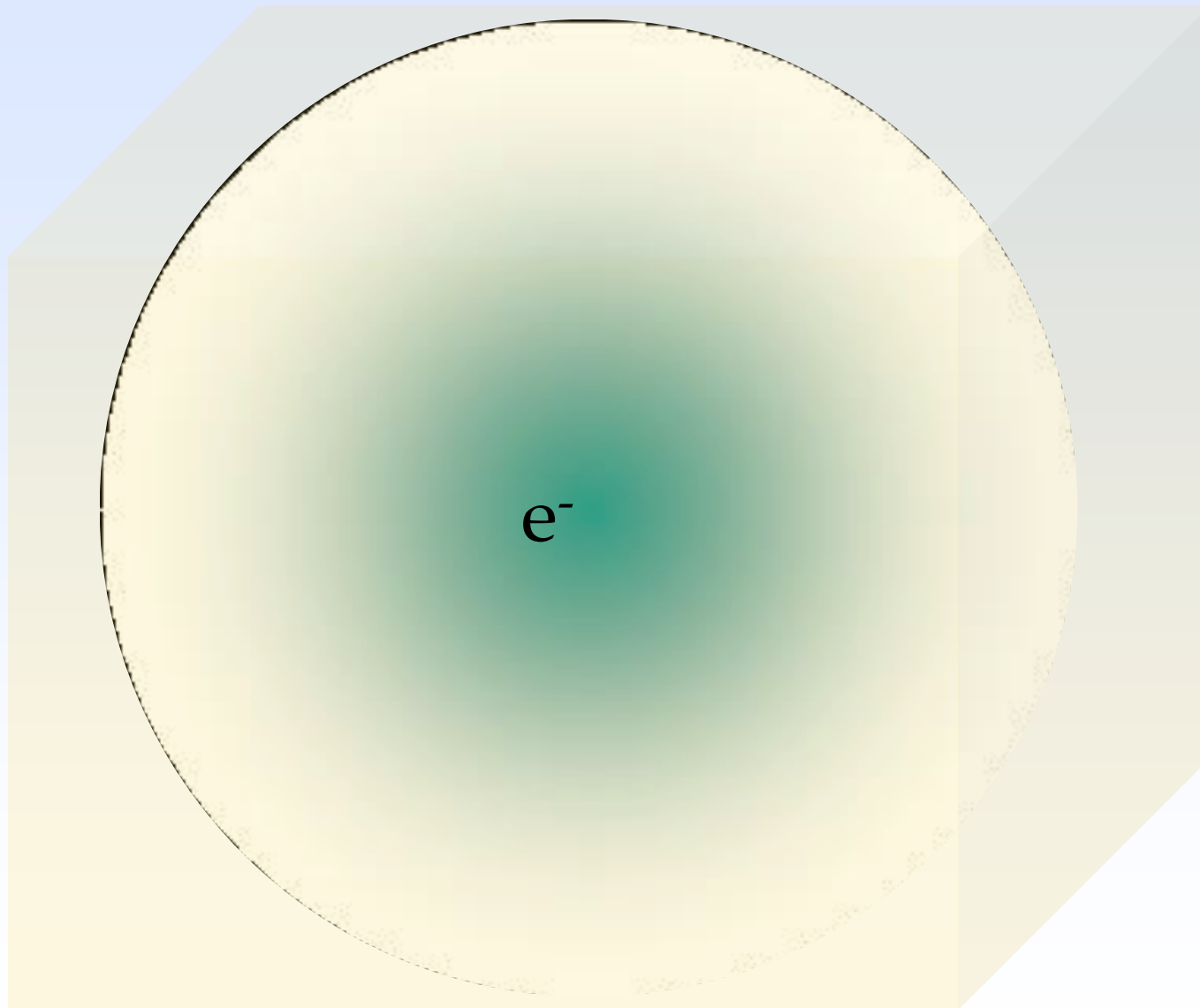
Principles and Varieties of Solar Energy (PHYS 4400)



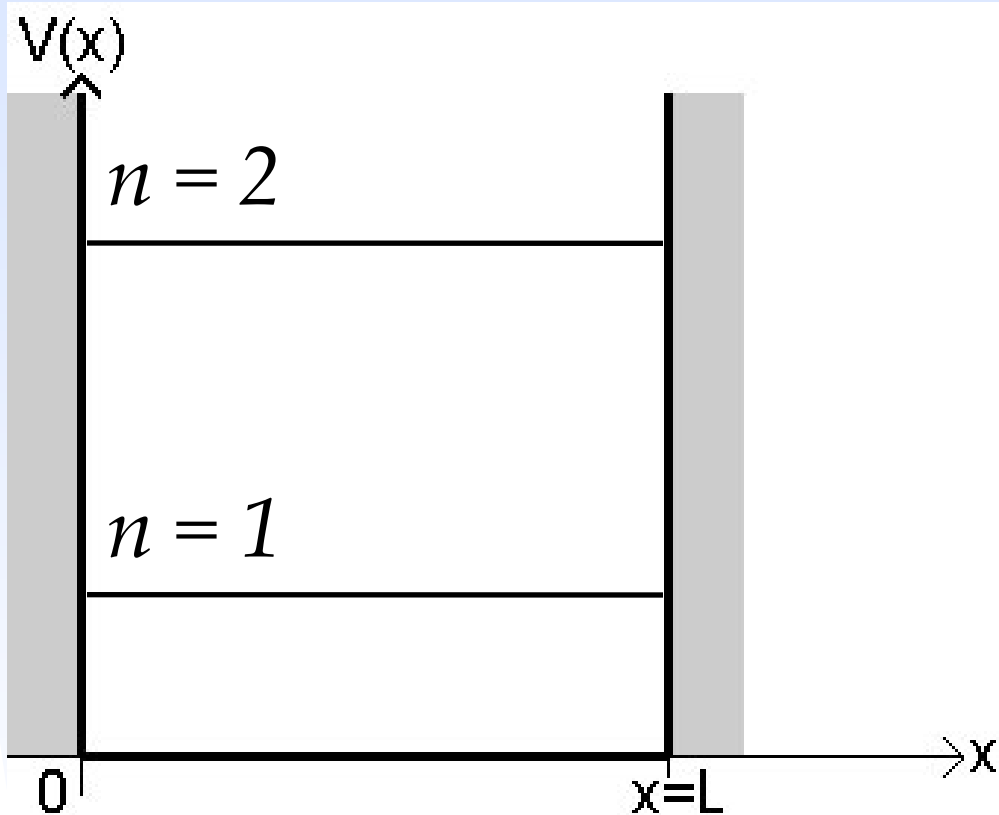
# Quantum confinement effect



## Quantum confinement effect (2)



# Particle in a box (quantum well)



$$E_n = \frac{\hbar^2 \pi^2}{2mL^2} n^2$$

The Potential,  $V(x)$ , is 0 inside the box, and infinite elsewhere (infinite barriers)



# Nanomaterials for solar energy conversion

- Enable high surface area devices →
  - strong light absorption (dye-sensitized nanostructured TiO<sub>2</sub>)
  - facilitates fast charge separation (proximity of photoexcited carriers to charge-separating interface)
- Customizable properties enable unique designs →
  - Engineerable (size-dependent) absorption spectrum
  - Varying geometries – e.g., efficient charge transport in quantum rods, nanotubes
  - Controlled chemical functionalization to direct charge separation
- Efficient multiple exciton generation

# Consequences of Quantization

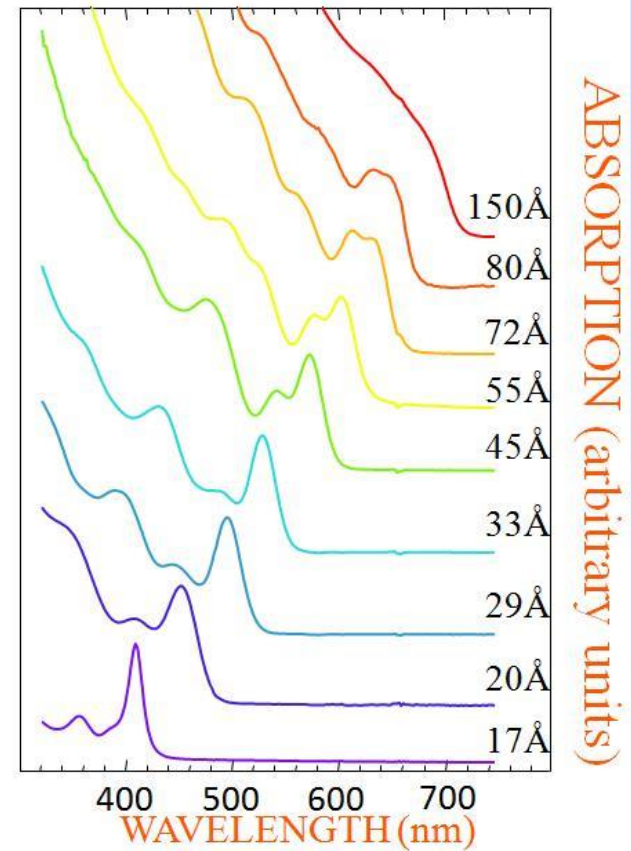
- *Dramatic variation of optical and electronic properties*
- *Large blue shift of absorption edge*
- *Discrete energy levels/structured absorption and photoluminescence spectra*
- *Enhanced photoredox properties for photogenerated electrons and holes*
- *Enhanced Inverse Auger (impact ionization, or multiple exciton generation)*
- *Slowed relaxation and cooling of photogenerated hot electrons and holes (controversial)*
- *PL blinking in single QDs*
- *Conversion of indirect semiconductors to direct semiconductors or vice versa*
- *Greatly enhanced non-linear optical properties*
- *Greatly modified pressure dependence of phase changes and direct to indirect transitions*
- *Efficient anti-Stokes luminescence*



# Size-dependent optical properties

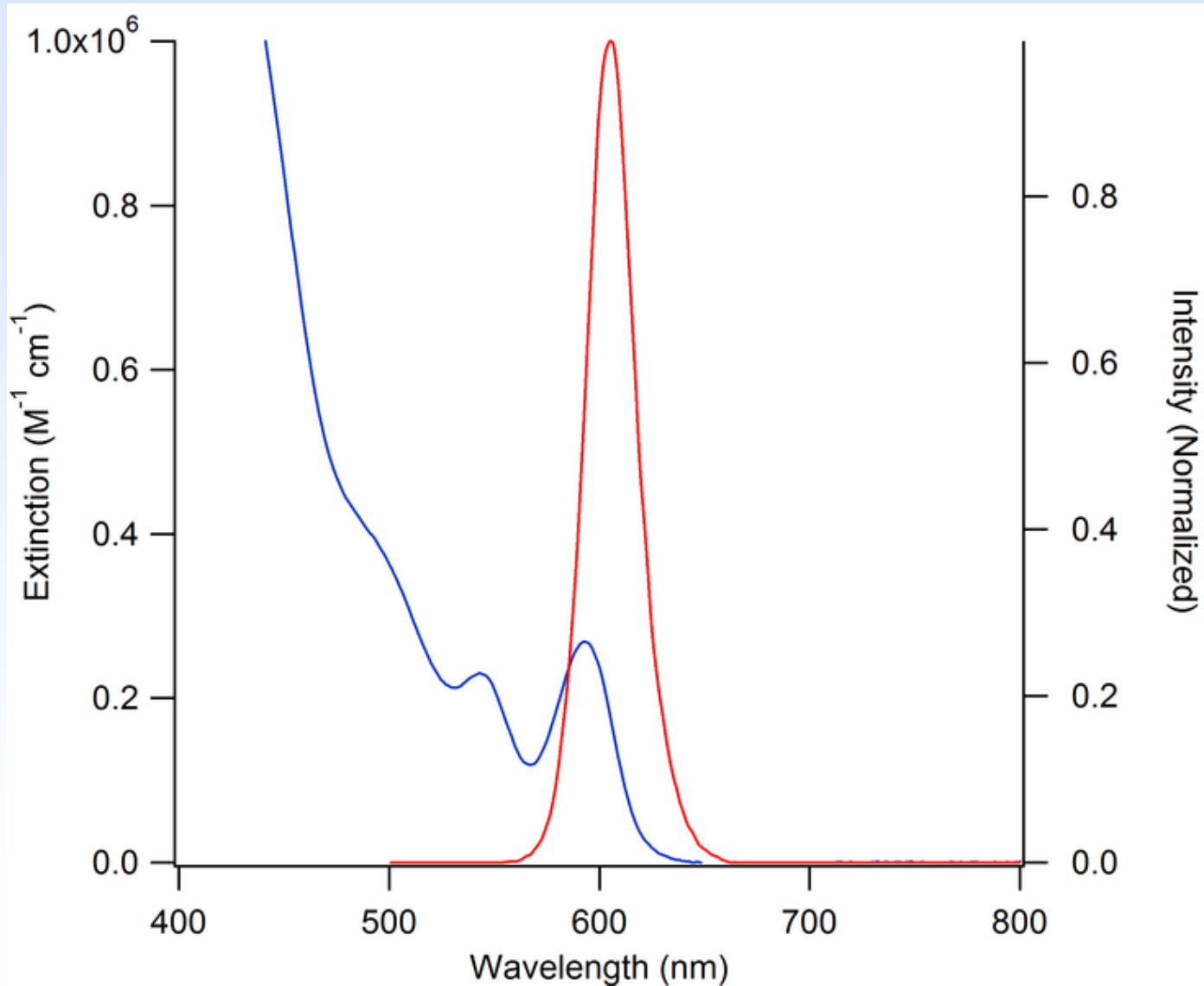
## Quantum Confinement

2 nm  $\xrightarrow{\text{CdSe}}$  8 nm



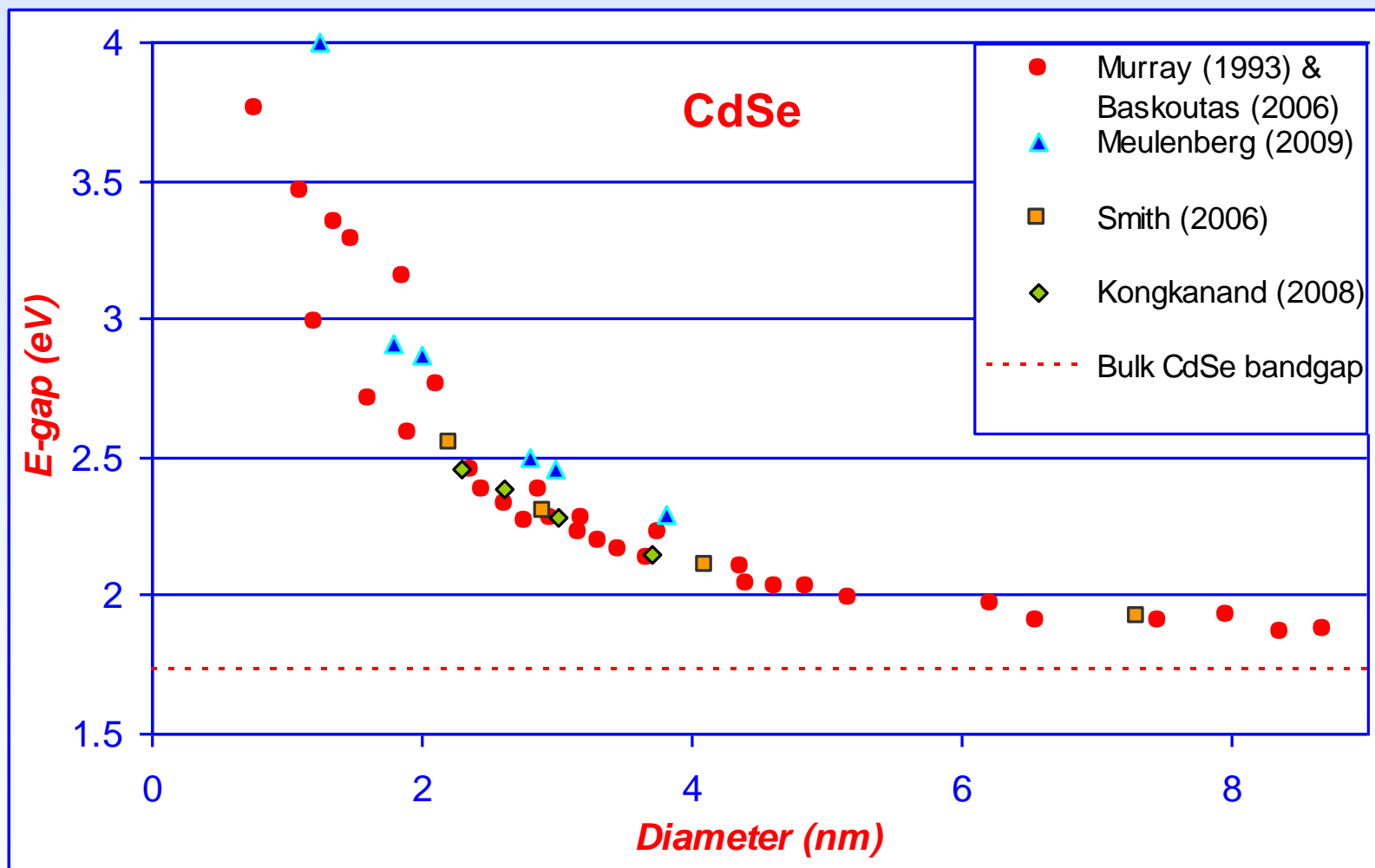
<http://nanocluster.mit.edu/research.php>

# Absorption and emission (CdSe nanocrystals)





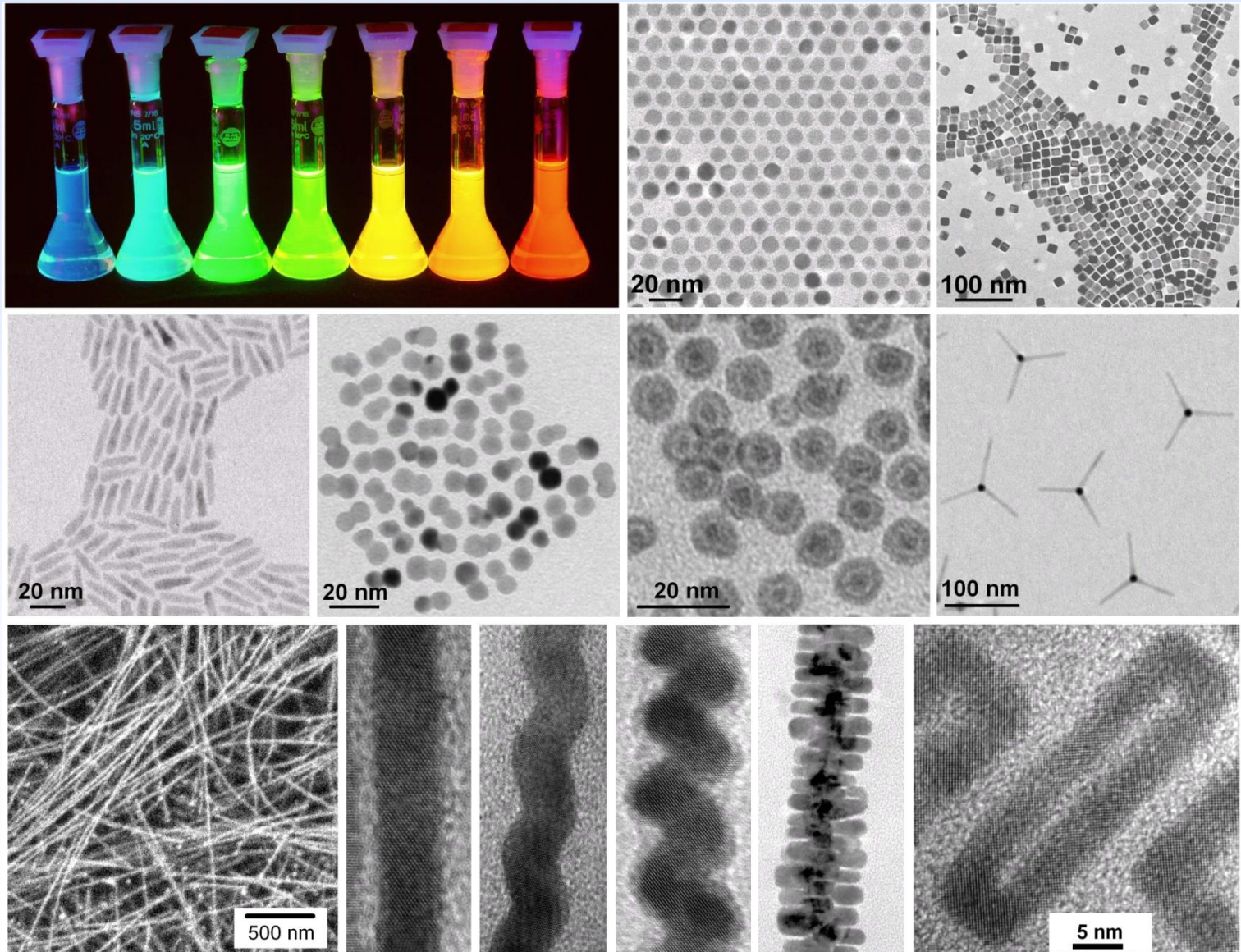
# Size-dependent bandgap of CdSe NCs



From "Physical and Optical Properties of Colloidal Semiconducting Nanocrystals for Solar Absorption", by Abdel Ibdah (UT)



# Colloidal nanostructures (crystalline)



<http://talapinlab.uchicago.edu>



# Quantum Confined Structures – Density of States

The number of states between  $k$  and  $k + dk$  in 3, 2, and 1 dimensions:

$$\frac{dN_{3D}}{dk} = 2 \left( \frac{L}{2\pi} \right)^3 4\pi k^2, \quad \frac{dN_{2D}}{dk} = 2 \left( \frac{L}{2\pi} \right)^2 2\pi k, \quad \frac{dN_{1D}}{dk} = 2 \left( \frac{L}{2\pi} \right)$$

$$g_{c,3D} = \frac{8\pi\sqrt{2}}{h^3} m_{eff}^{3/2} \sqrt{E - E_{min}}$$

$$g_{c,2D} = \frac{4\pi m_{eff}}{h^2}$$

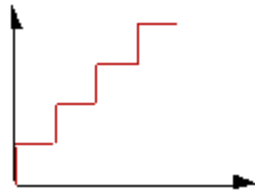
$$g_{c,1D} = \sqrt{\frac{2\pi m_{eff}}{h^2}} \frac{1}{\sqrt{E - E_{min}}}$$



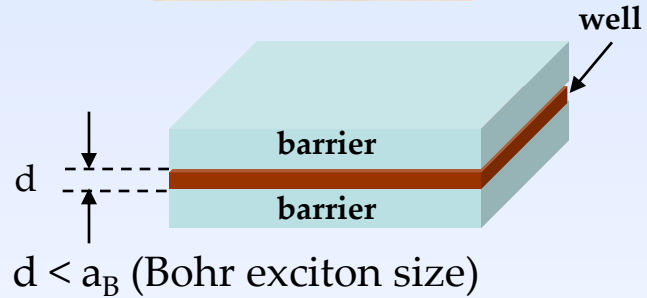
# Quantum confinement effect on density of electronic states



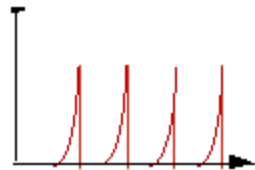
Bulk Semiconductor



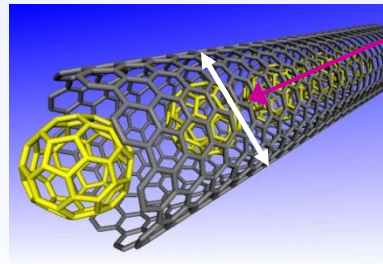
Quantum Well



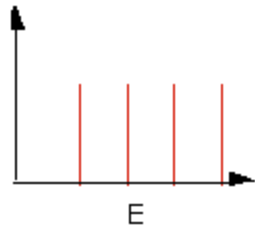
$N(E)$



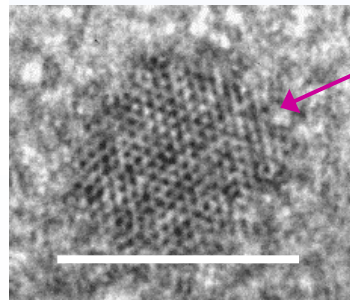
Quantum Wire



~1 nm



Quantum Dot  
(or Nanocrystal)



~6 nm dia.

60 Å InP QD

Dimensionality

3D

2D

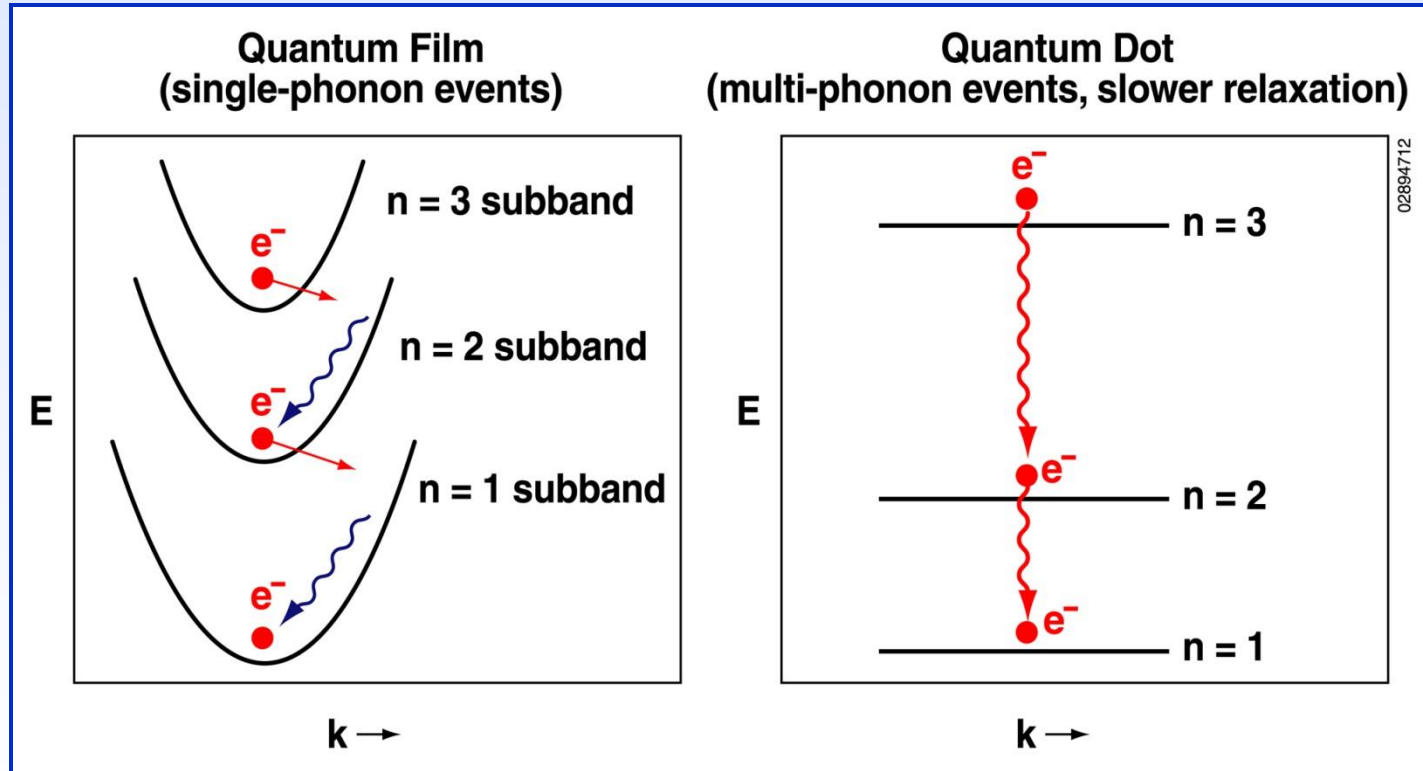
1D

0D



# Hot electron relaxation pathways

## Quantum Films vs Quantum Dots



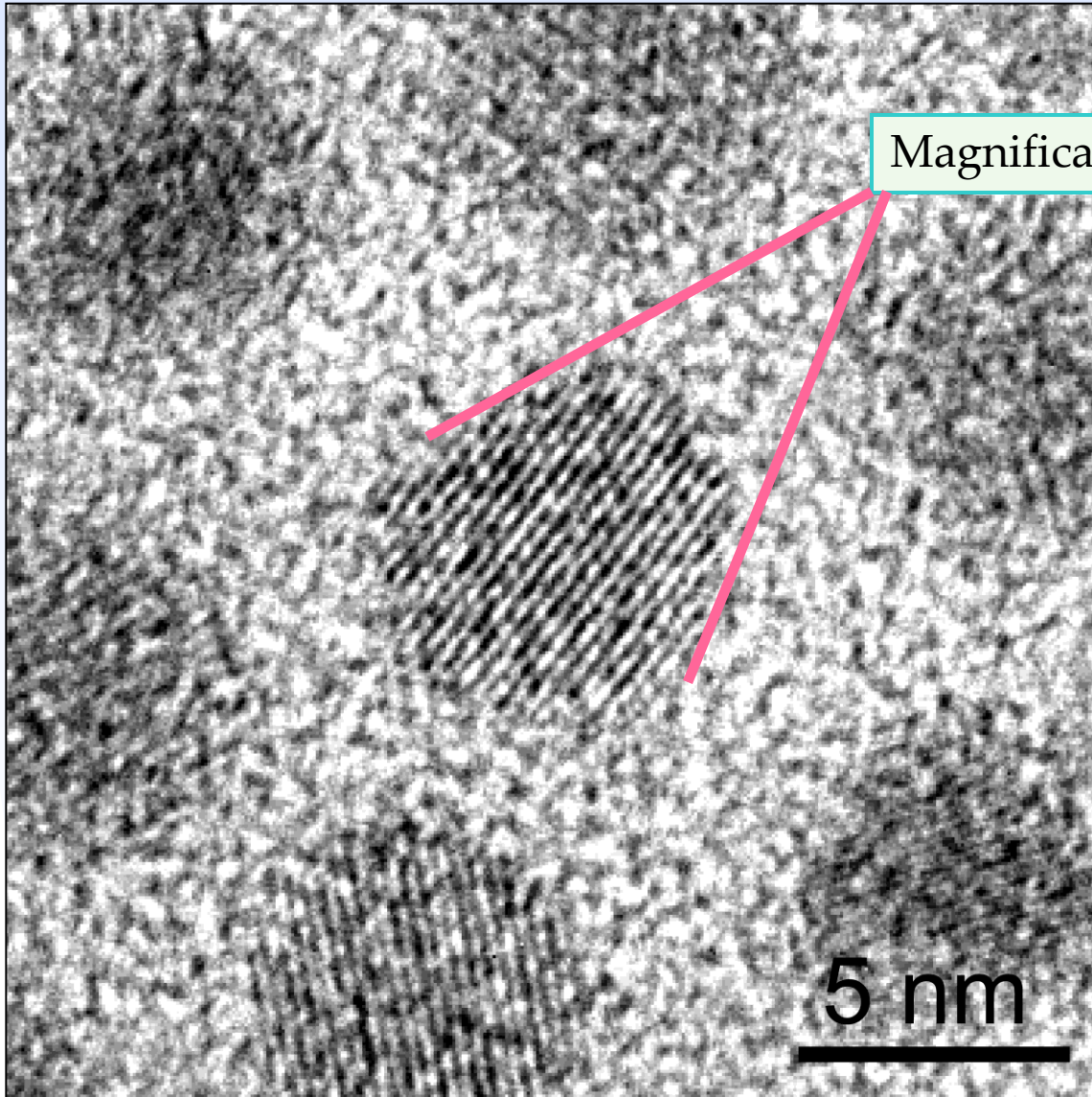
phonon bottleneck



# Transmission electron micrograph (TEM) of Lead Selenide NCs

PbSe

Magnification ~ 2,000,000x



# Synthesis of colloidal nanocrystals

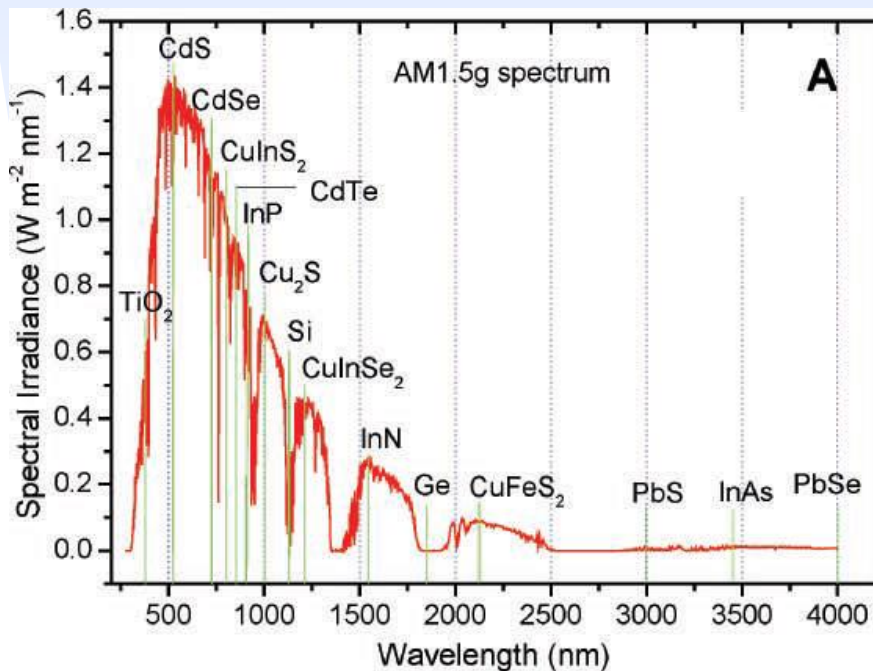


Typical three-headed flask set up. The middle head is connected to the Schlenk line's glass manifold. The left head is covered with a septum pierced by the thermocouple. The right head is for injection. Photo and caption courtesy of T. Kinner (UT).

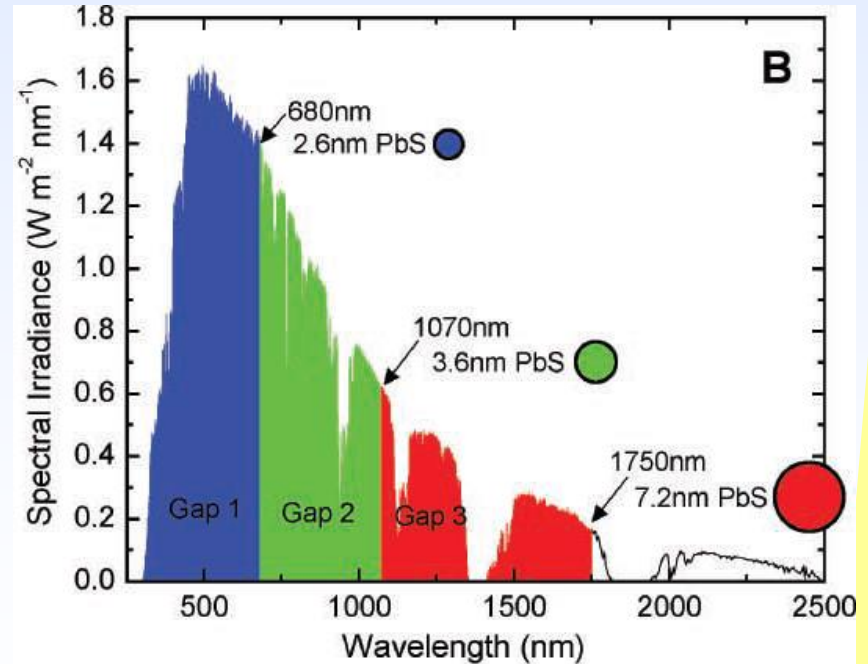


# Why pursue QD solar cells?

1. Colloidal synthesis produces high-quality nanocrystals
2. Solution processed, tunable band-gap
3. Potentially easy to process (**room temperature, ambient air**)
4. Scientifically interesting: balance quantum confinement w/ transport
5. Flexibility (?)



AM1.5G solar spectrum along with some common bulk semiconductors band-gaps



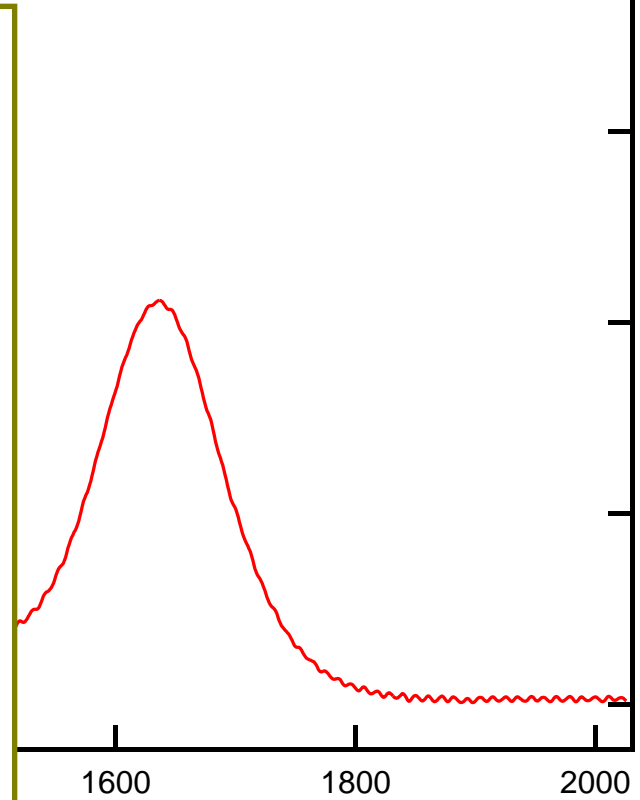
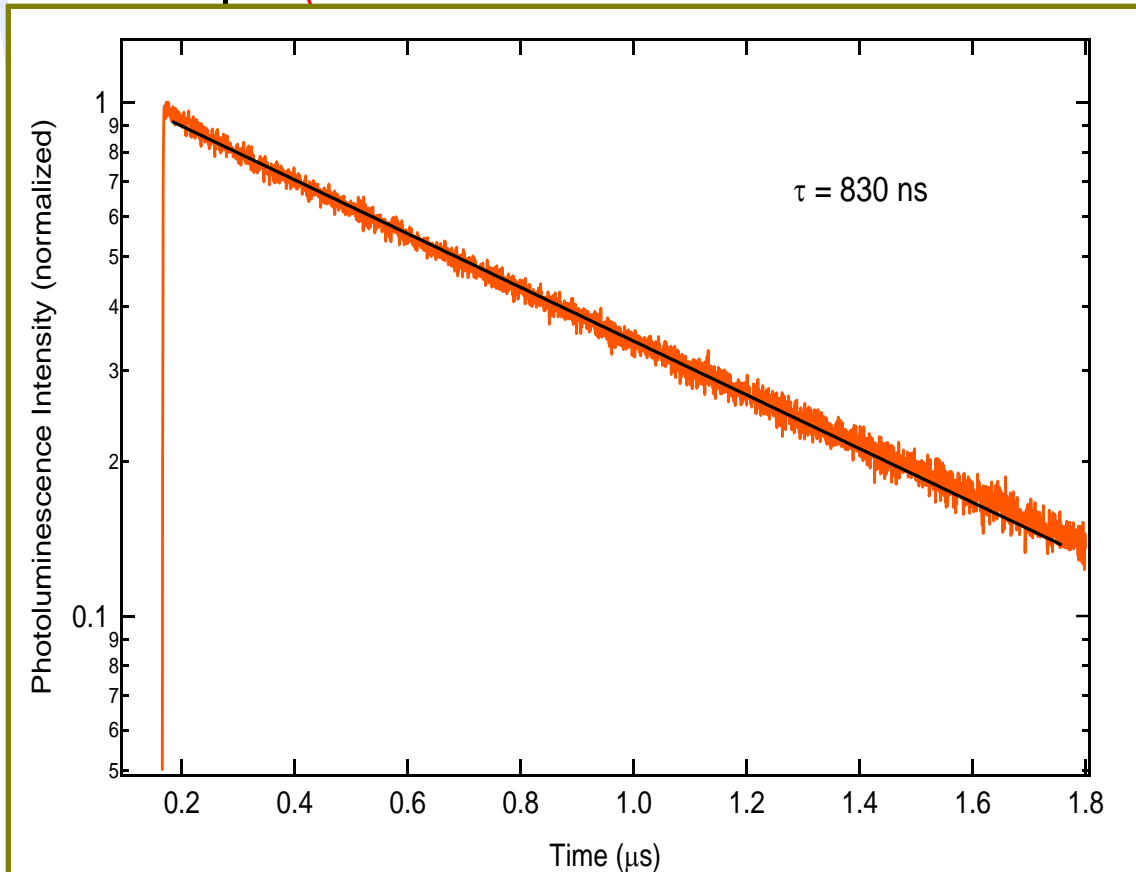
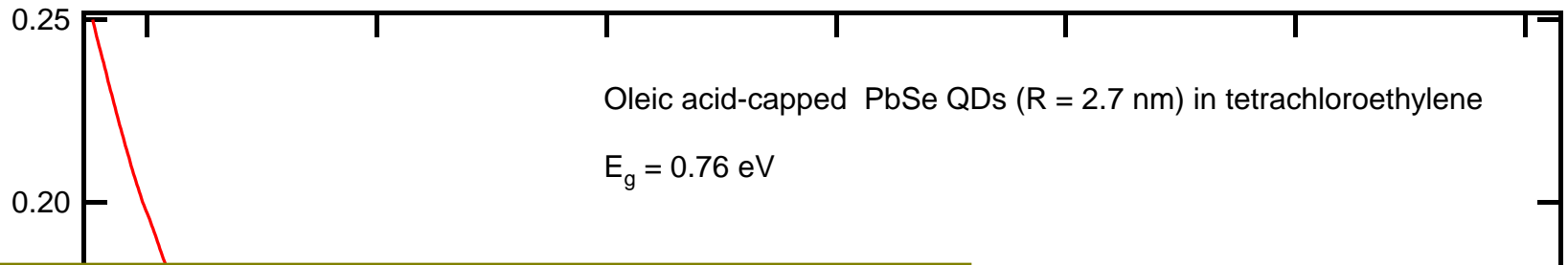
Triple junction PbS dot size

J. Tang, et al., *Adv. Mater.* 22,1(2010)

.... energizing Ohio for the 21st Century



# Colloidal PbSe QDs in tetrachloroethylene (TCE)

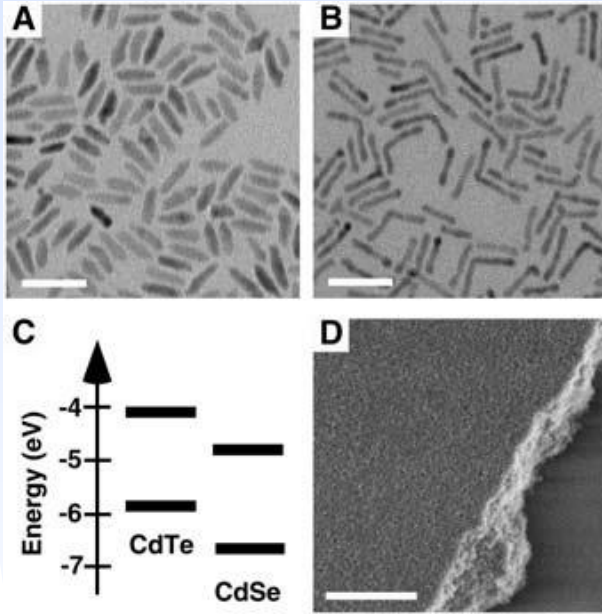


# Annealed NC-based solar cell

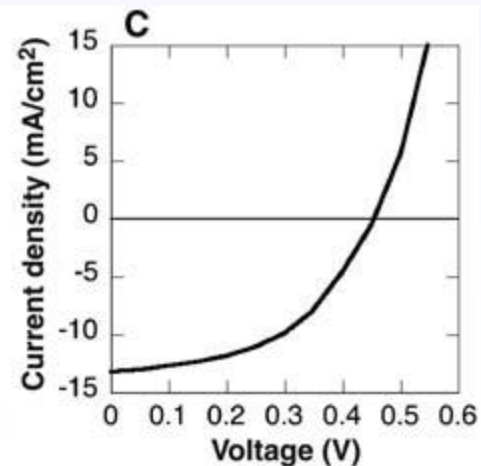
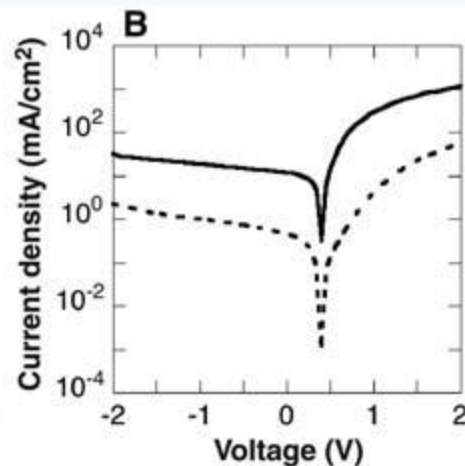
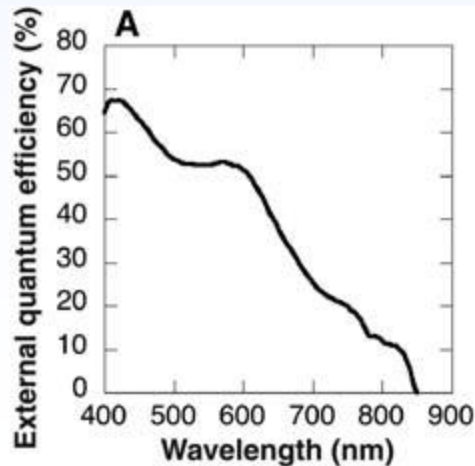
## *Air-Stable All-Inorganic Nanocrystal Solar Cells Processed from Solution*

Ilan Gur, Neil A. Fromer, Michael L. Geier, A. Paul Alivisatos

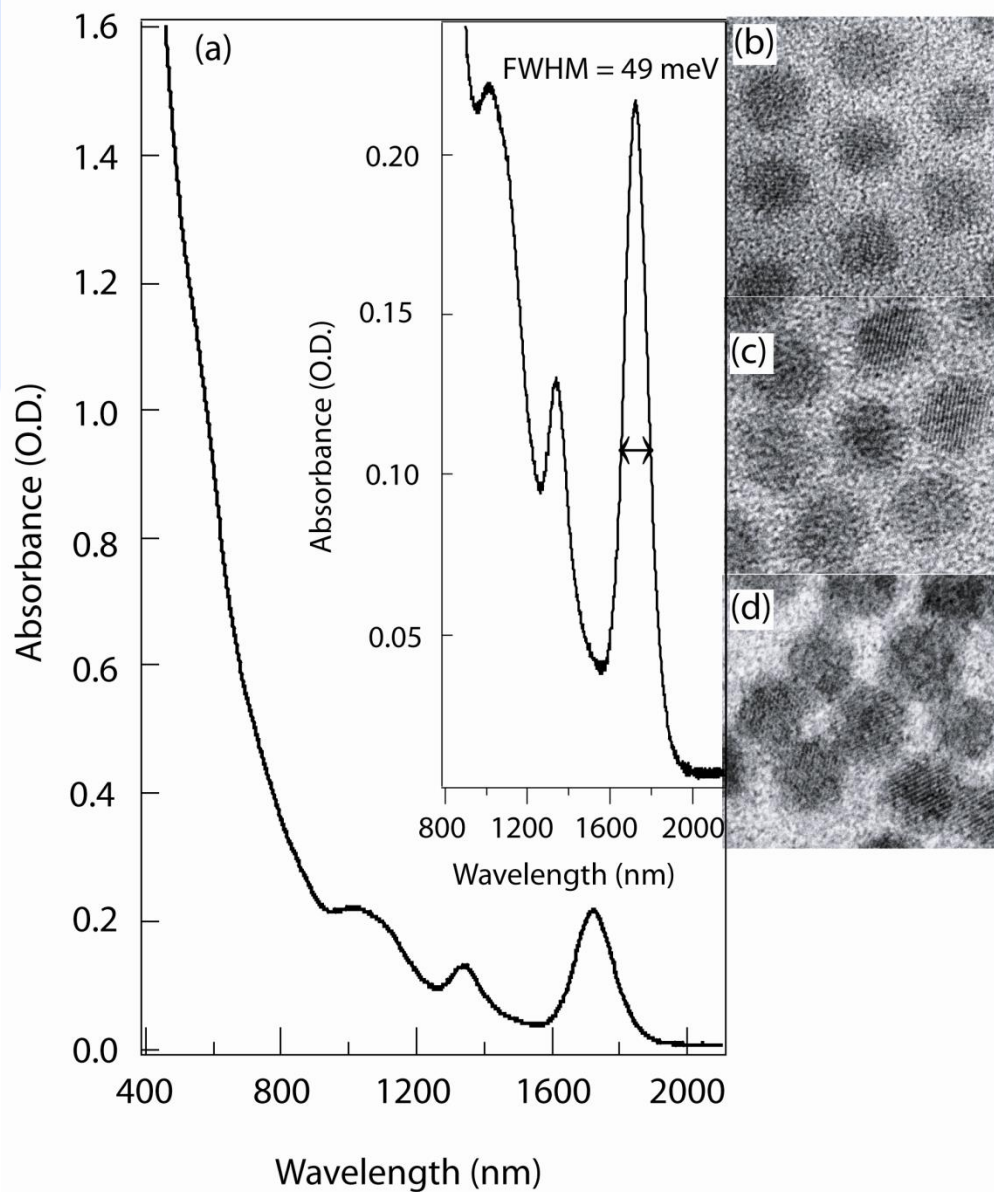
21 OCTOBER 2005 VOL 310 SCIENCE



Transmission electron micrographs of (A) CdSe and (B) CdTe NCs used in this investigation. Scale bar, 40 nm. (C) An energy diagram of valence and conduction band levels for CdTe and CdSe illustrates the type II charge-transfer junction formed between the two materials...



# Drop-cast films of 5.7 nm dia. PbSe NCs



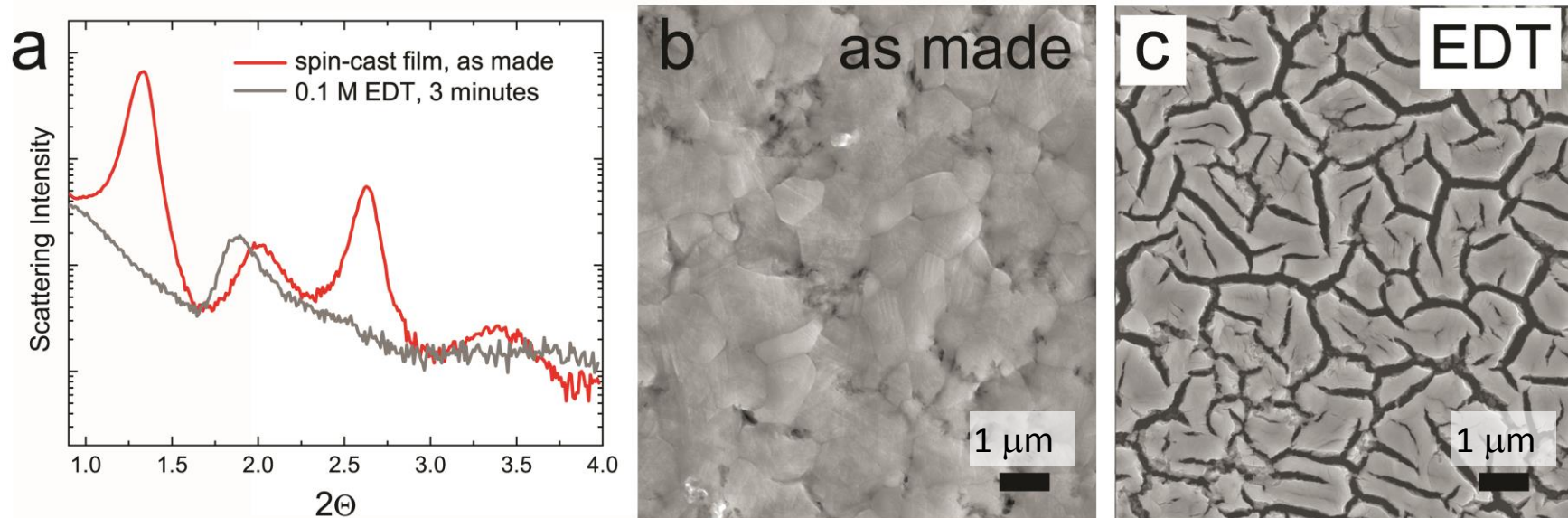
oleic acid (1.8 nm)

aniline (0.8 nm)

ethylenediamine (0.4 nm)

J. E. Murphy *et al.*, JACS **128**, 3241 (2006).

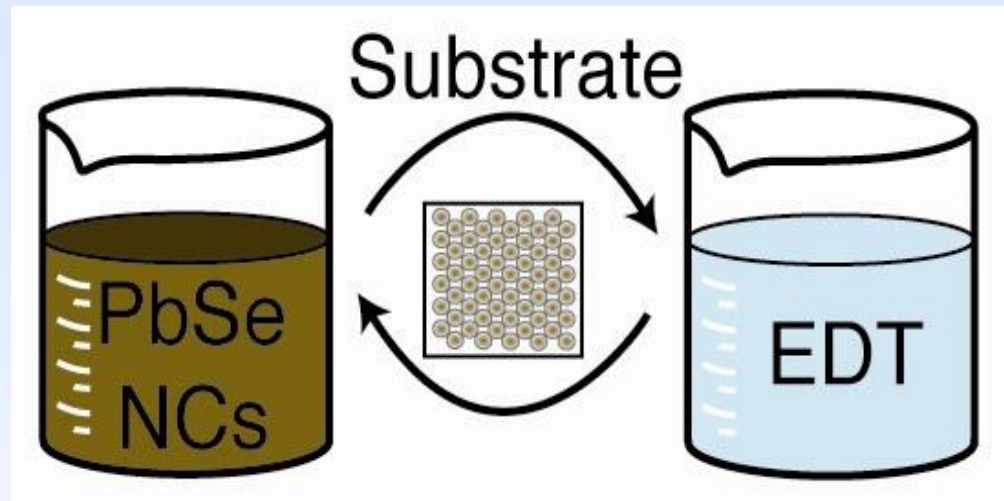
# Post-casting treatment of spin-cast films of PbSe NCs



“Microstructure of the spin-cast NC films before and after EDT treatment. (a) SAXS data, showing a  $\sim 16$  Å decrease in the spacing between the NCs and a dramatic loss of superlattice order upon EDT treatment. Measurements were taken in air. (b, c) Plan-view SEM images of (b) an untreated film and (c) a treated film.”

J. Luther, M. Law et al., ACS Nano 2, 271 (2008).

# Layer-by-layer fabrication of PbSe NC films

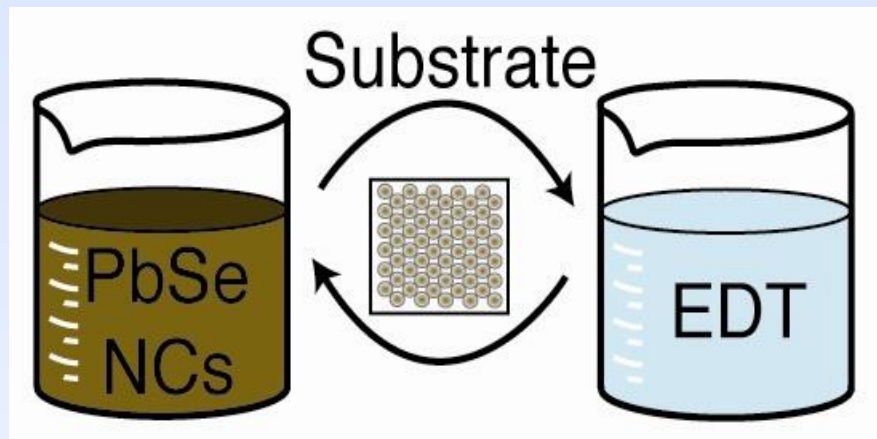


EDT = 1,2-ethanedithiol

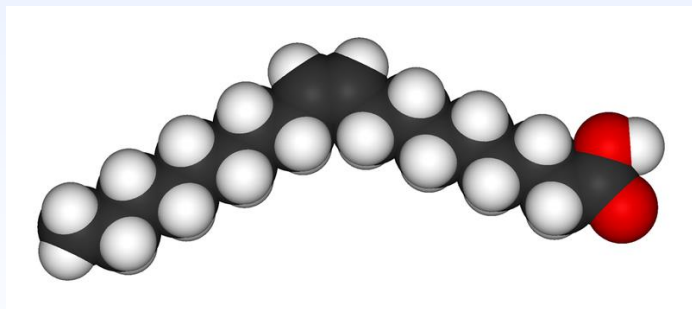
**Layer by layer (LbL) fabrication of PbSe nanocrystal (NC) films.** Nanocrystal films prepared by dip-coating, alternating between (1) PbSe NCs in hexane and (2) 0.1 M EDT in anhydrous acetonitrile, allowing the film to dry between each layer.

J. M. Luther, M. Law *et al.*, "Structural, Optical, and Electrical Properties of Self-Assembled Films of PbSe Nanocrystals Treated with 1,2-Ethanedithiol", *ACS Nano* **2**, 271 (2008).

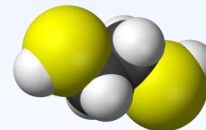
# Ligand exchange in PbX NC films



EDT = 1,2-ethanedithiol

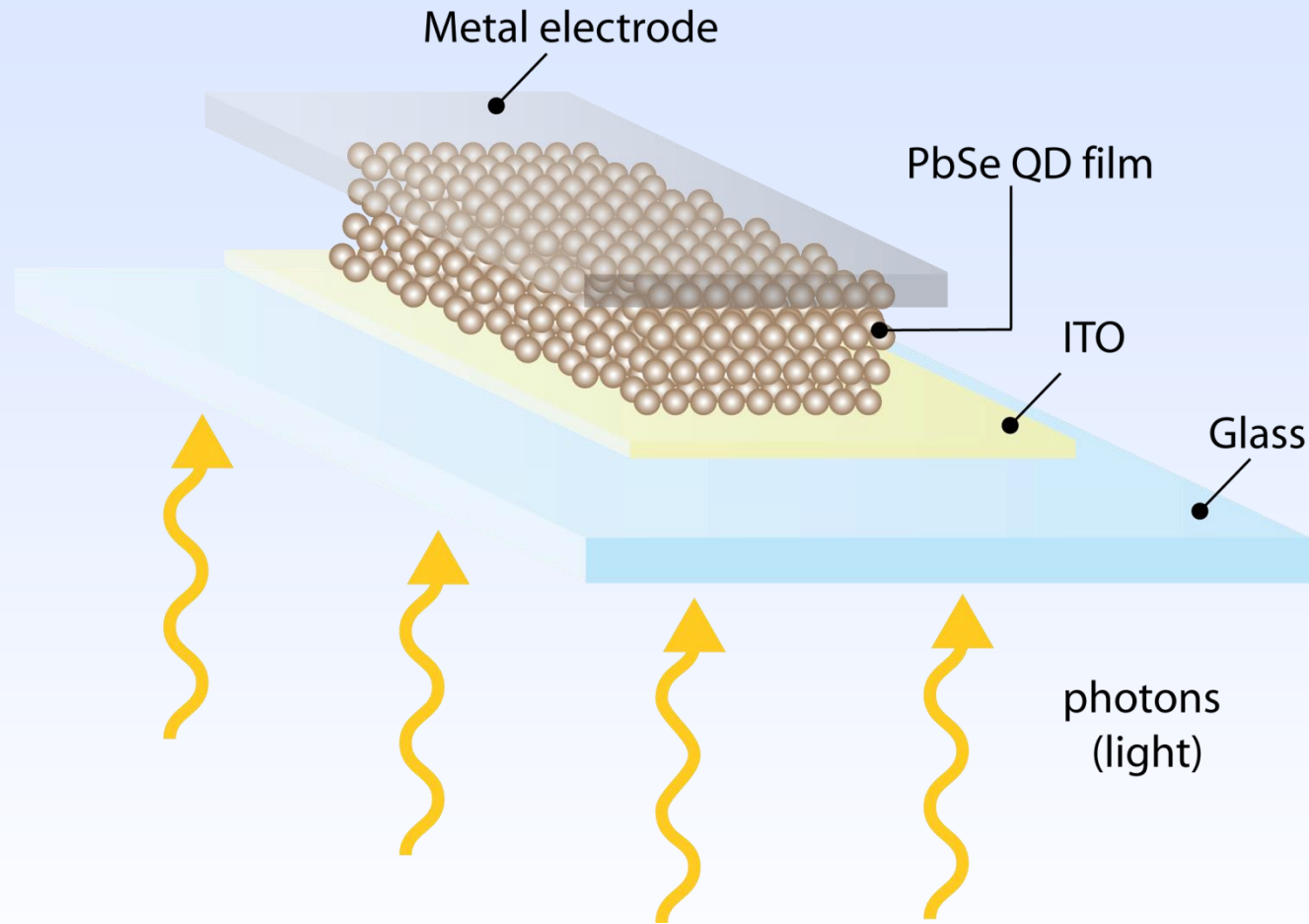


Oleic acid,  $C_{18}H_{34}O_2$   
 $L \approx 20 \text{ \AA}$



1,2-ethanedithiol  
 $C_2H_6S_2$   
 $L \approx 6 \text{ \AA}$

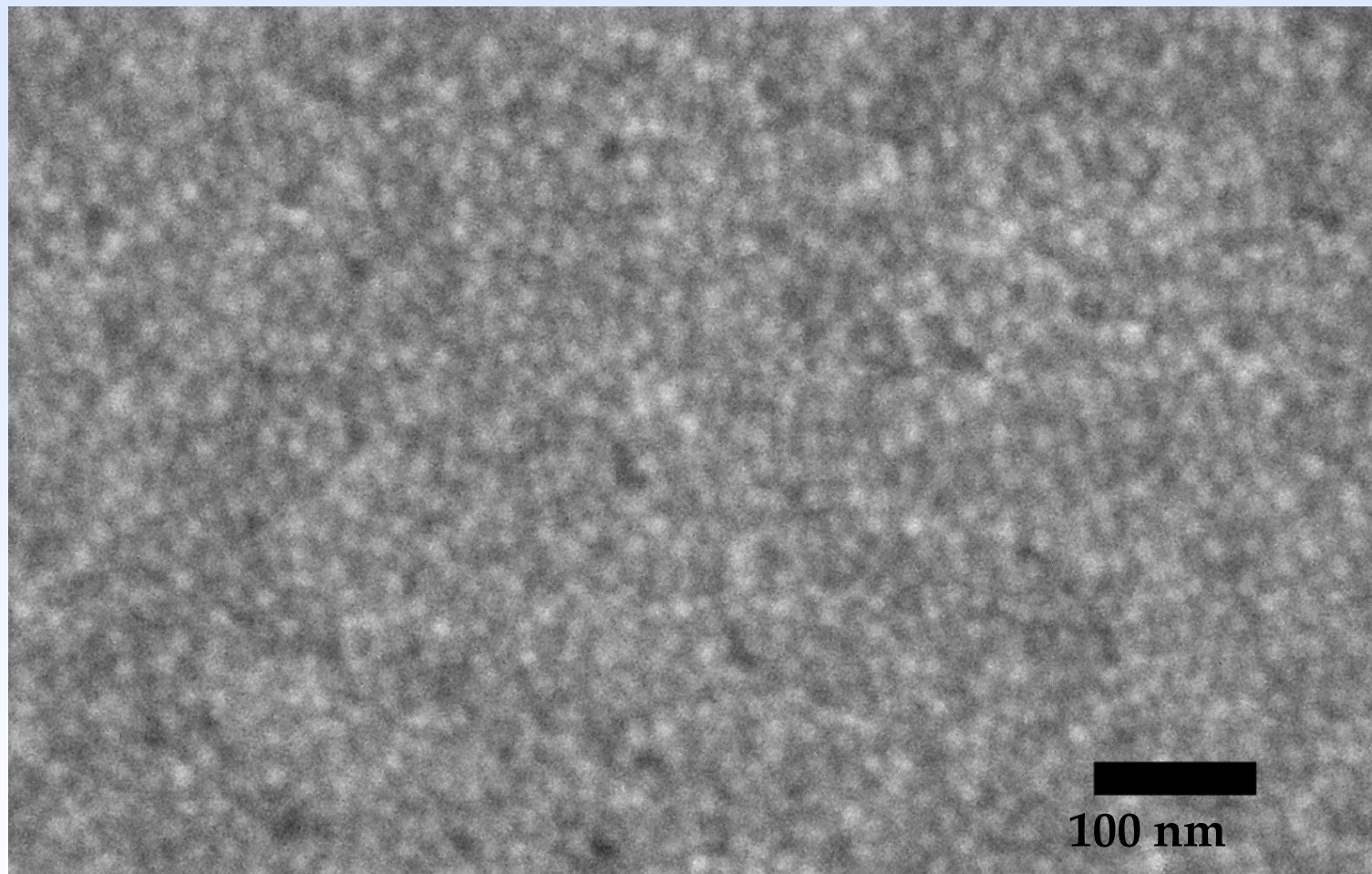
# Schottky barrier nanocrystal-based solar cell



- For MEG: Auger recombination typically occurs on  $\lesssim 100$  ps timescale (need fast exciton dissociation and/or diffusion to low density)
- High long-range mobility desired
- EQE > 100% would provide MEG process/concept confirmation



# Layer-by-layer dip-coated PbSe films



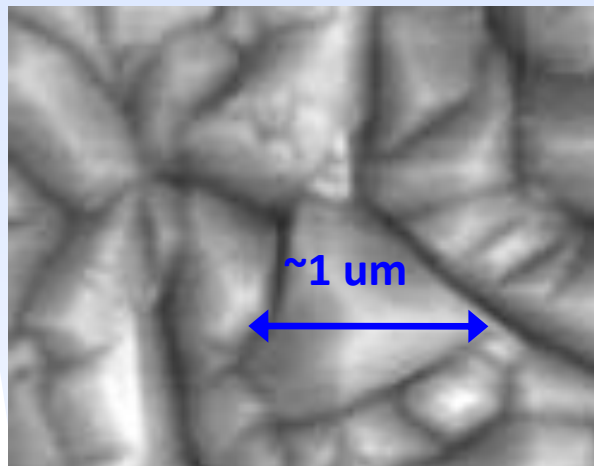
Plan view SEM image of PbSe NC films prepared by layer-by-layer dip coating onto ITO substrate. LbL film shown was produced using 10-20 dip coating cycles.

J. Luther, M. Law *et al.*, *ACS Nano* **2**, 271 (2008).

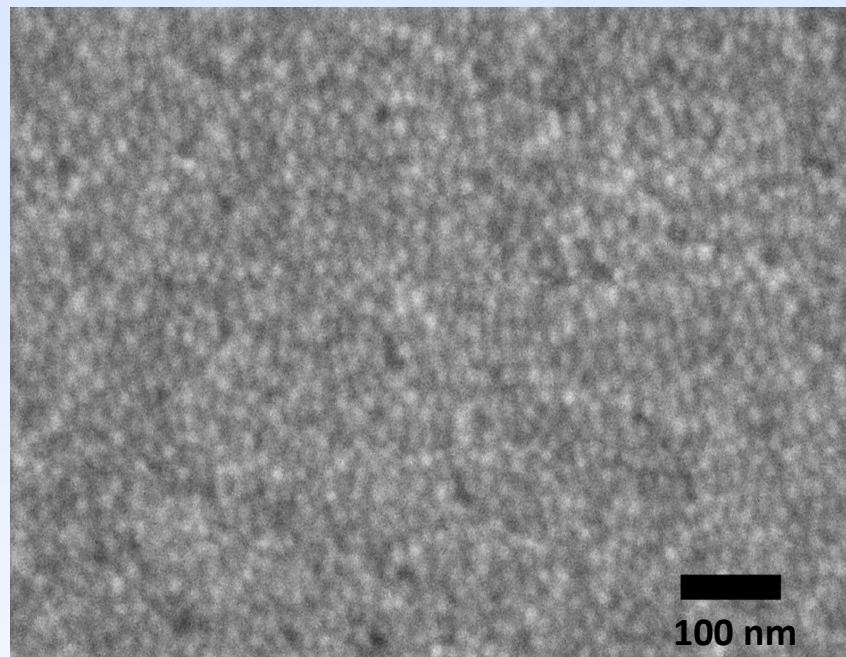




# “Grain boundary” density considerations



e.g. CdTe



Estimating effective “grain boundary densities” (boundary area / layer area)

**CdTe:**  $\sim 1 \mu\text{m}$  grain size (assumed cubic grains,  $\sim 1 \mu\text{m}$  thick layer):

**3 ( $\mu\text{m}^2 / \mu\text{m}^2$ )**

**PbSe QD film:**  $\sim 5 \text{ nm}$  “grain size” (assumed cubic grains 5 nm on a side,  $1 \mu\text{m}$  thick film):

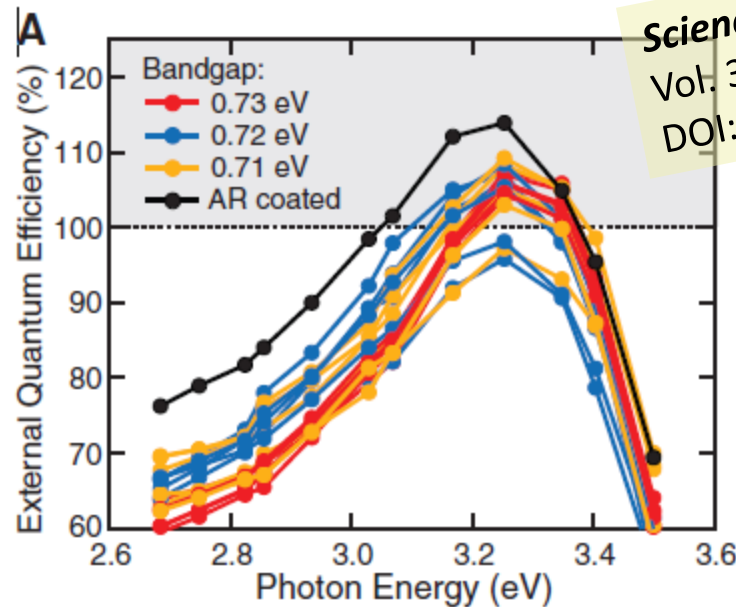
**600 ( $\mu\text{m}^2 / \mu\text{m}^2$ )**

$$S/V \propto 1/r$$



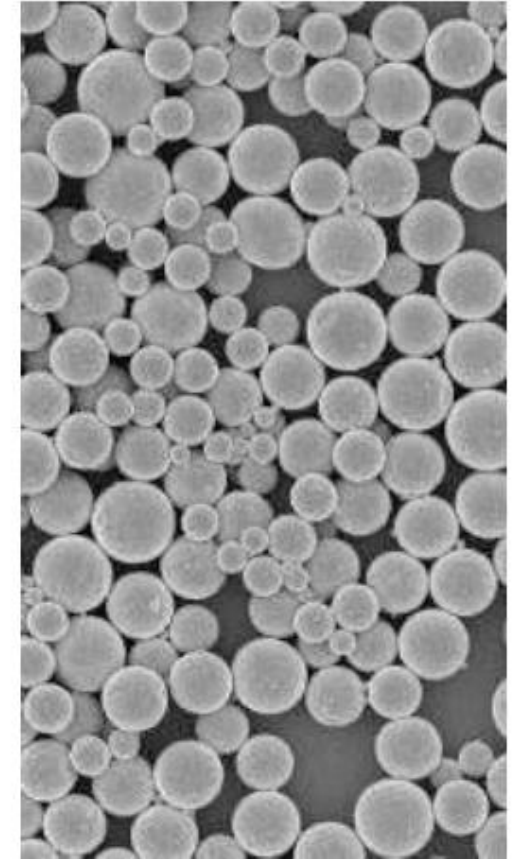
# Peak External Photocurrent Quantum Efficiency Exceeding 100% via MEG in a Quantum Dot Solar Cell

Octavi E. Semonin,<sup>1,2</sup> Joseph M. Luther,<sup>1</sup> Sukgeun Choi,<sup>1</sup> Hsiang-Yu Chen,<sup>1</sup> Jianbo Gao,<sup>1,3</sup> Arthur J. Nozik,<sup>1,4\*</sup> Matthew C. Beard<sup>1\*</sup>



*Science* 16 December 2011:  
Vol. 334 no. 6062 pp. 1530-1533  
DOI: 10.1126/science.1209845

## Roll-to-roll processing from solution source (e.g., Nanosolar CIGS)



**Figure 6 and 7:** A laboratory sample of our nanoparticle ink. Nanoparticles shown to the right are an average of 20nm in diameter.

from NanoSolar white paper



# Good solar cells from nanoparticle inks (CIGS)

Nanosolar

## CdS/Cu(In,Ga)Se<sub>2</sub> Cell

Device ID: H09B071-01C #2

Device Temperature: 24.0

Apr 09, 2009 12:31

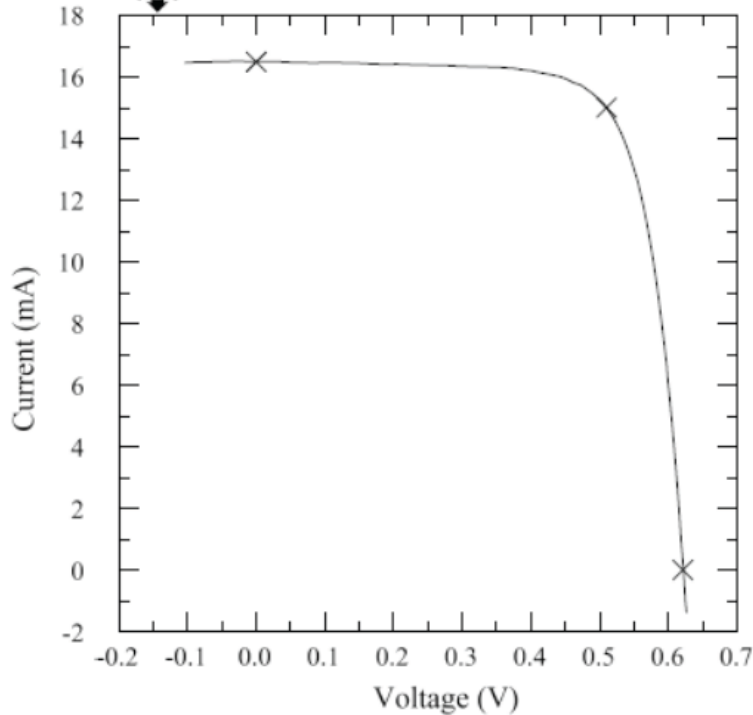
Device Area: 0.5000 cm<sup>2</sup>

Spectrum: ASTM G173 global

Irradiance: 1000.0 W/m<sup>2</sup>



X25 IV System Confidential  
PV Performance Characterization Team



$V_{oc} = 0.6214 \text{ V}$   
 $I_{sc} = 16.490 \text{ mA}$   
 $J_{sc} = 32.980 \text{ mA/cm}^2$   
Fill Factor = 74.70 %

$I_{max} = 15.010 \text{ mA}$   
 $V_{max} = 0.5101 \text{ V}$   
 $P_{max} = 7.6540 \text{ mW}$   
Efficiency = 15.31 %

from NanoSolar white paper

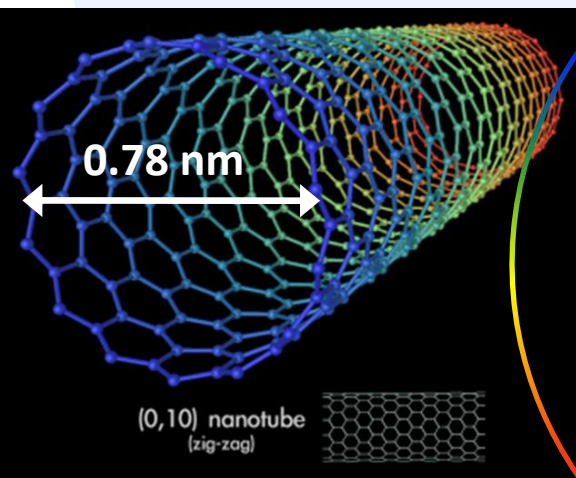


# Colloidal semiconductor nanocrystals

- Solution synthesis, typically at elevated temperature
- Inorganic crystalline core surrounded by organic capping molecules
- Most frequently suspended in organic solvents
- Can be stored stably either in powder or solution form

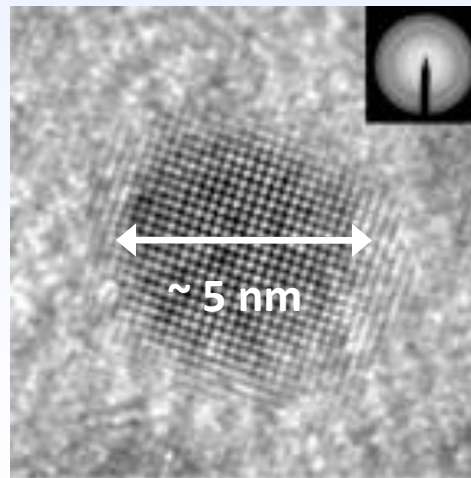
Colloidal semiconductor NCs have typical diameters of 1 nm to 10 nm

SWNT (10,0)



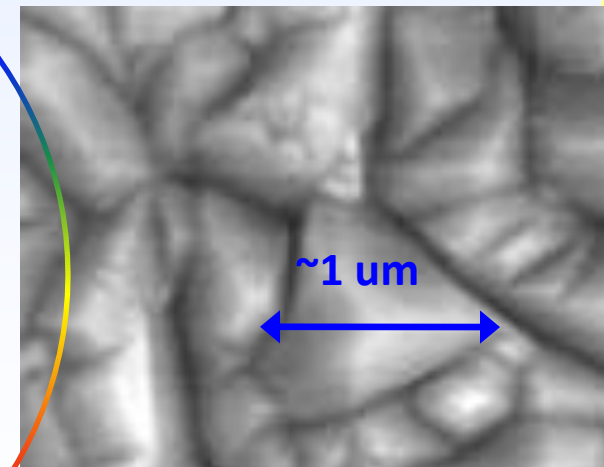
[http://commons.wikimedia.org/wiki/Main\\_Page](http://commons.wikimedia.org/wiki/Main_Page)

PbS NC



Sargent, *Adv. Mat.* (2005), 515-522.

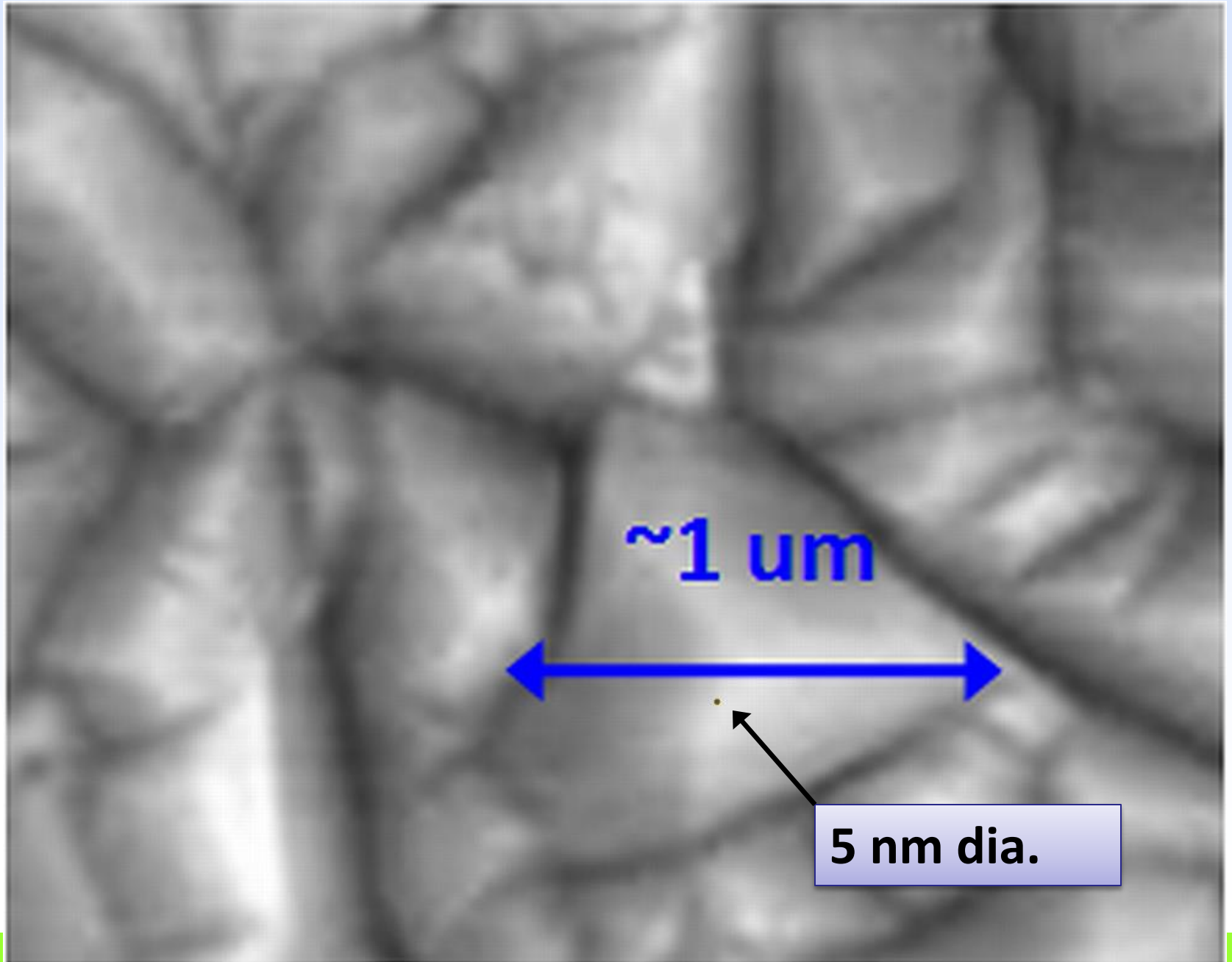
CdTe grain size (CSS)



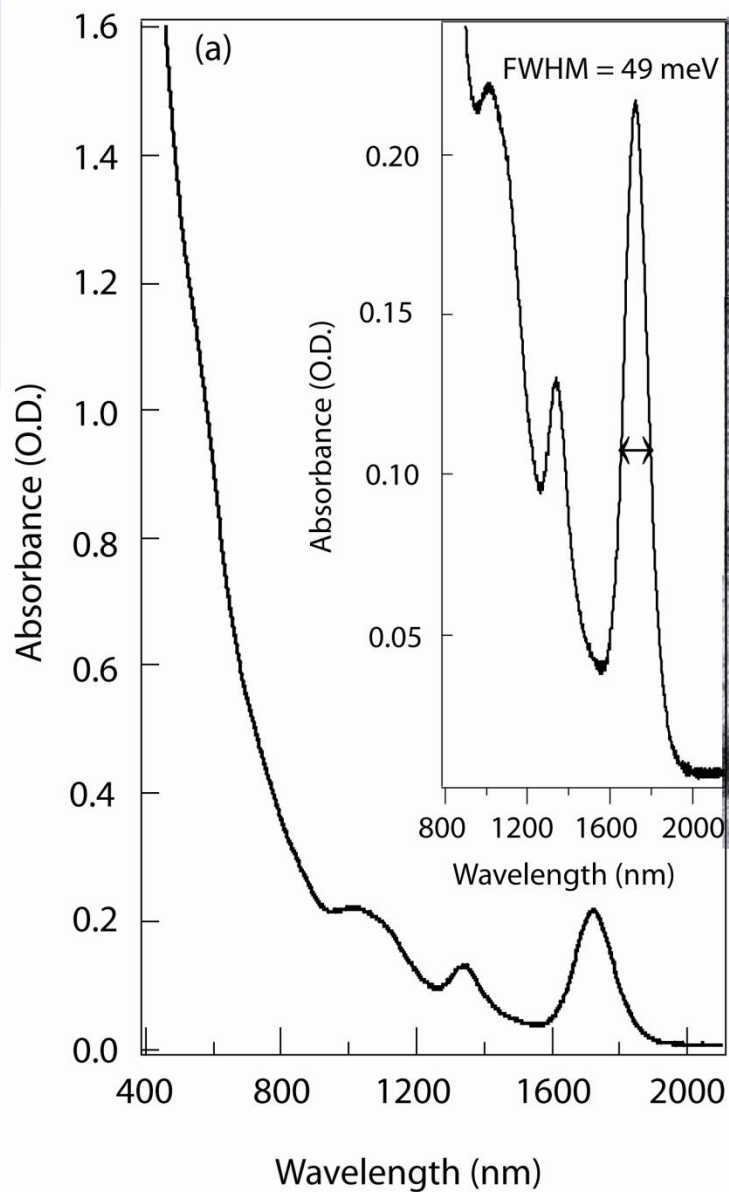
Quiñones et al., *J. Mater. Sci: Mat. Electron* (2007), 1085–1091



# Colloidal quantum dot – scale



# Post-deposition treatment of drop-cast films of 5.7 nm dia. PbSe QDs



oleic acid (1.8 nm)

aniline (0.8 nm)

ethylenediamine (0.4 nm)

Artemyev *et al.*, J. Phys. Chem. B 2000, 11617.

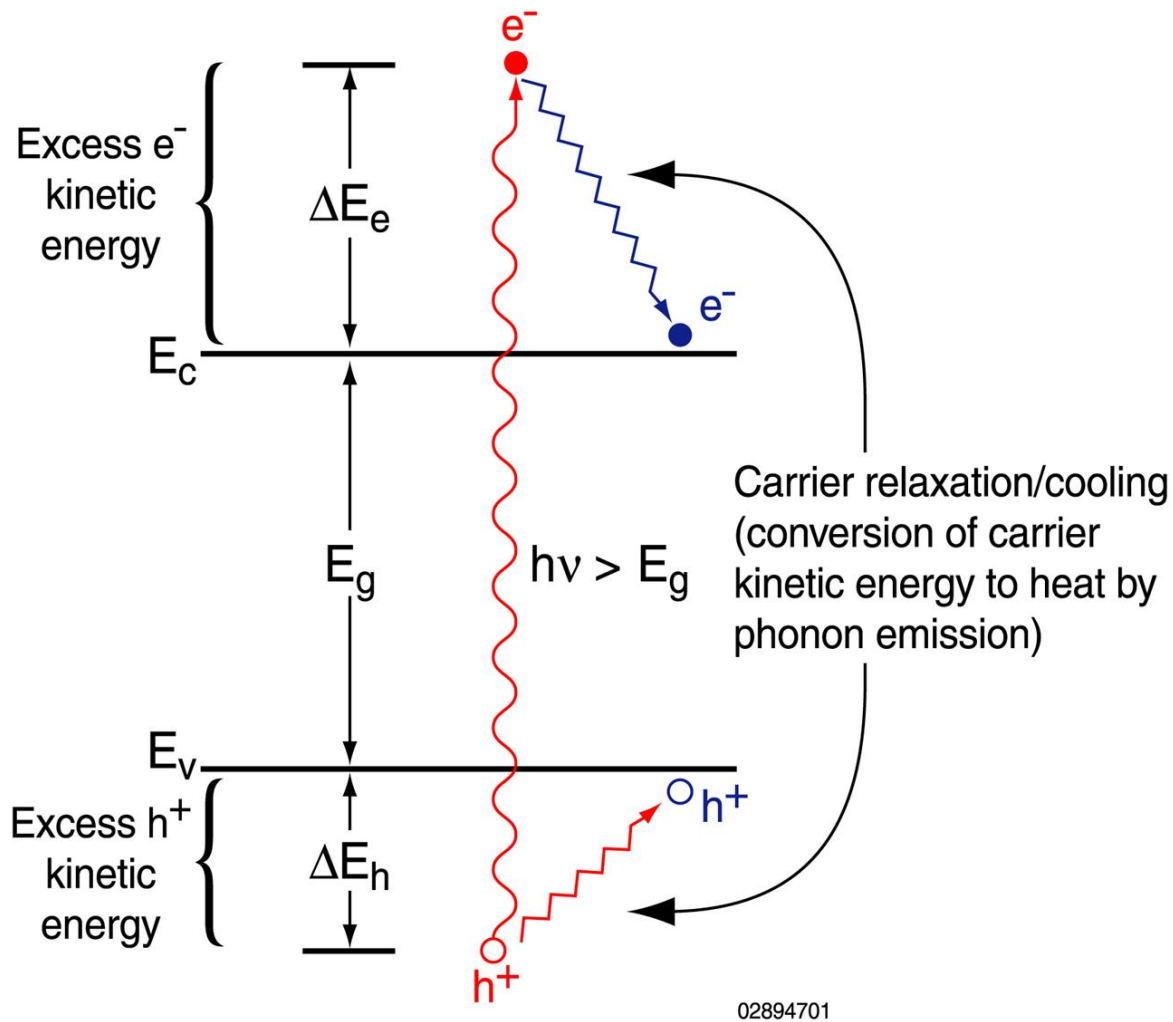
J. E. Murphy *et al.*, J. Phys. Chem. B 2006, 25455.

# Recent Progress in QD Solar Cells





# Thermalization losses



For  $c$ -Si ( $E_g = 1.1$  eV)  
at  $T = 300$  K, AM1.5G

$$\eta_{max} = 32.9\%$$

Losses

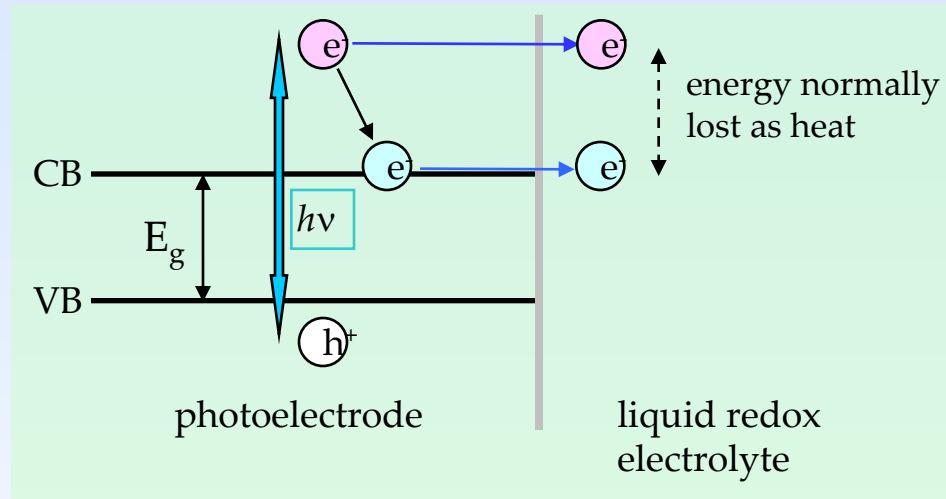
transmission = 18.7%

radiative em. = 1.6%

**heat** = 46.8%

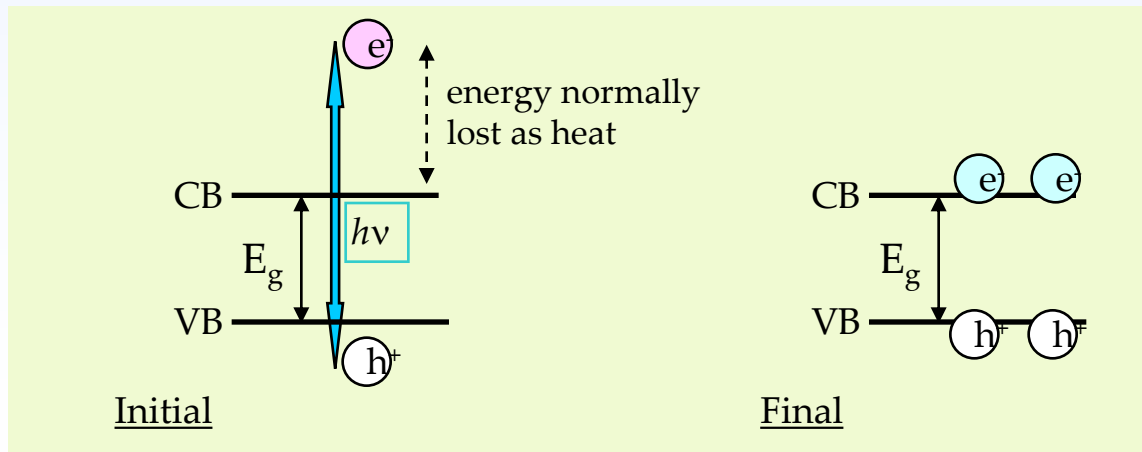
# Utilize photogenerated hot electrons to increase efficiency

## 1. **Higher photovoltage:** extract and utilize hot electrons



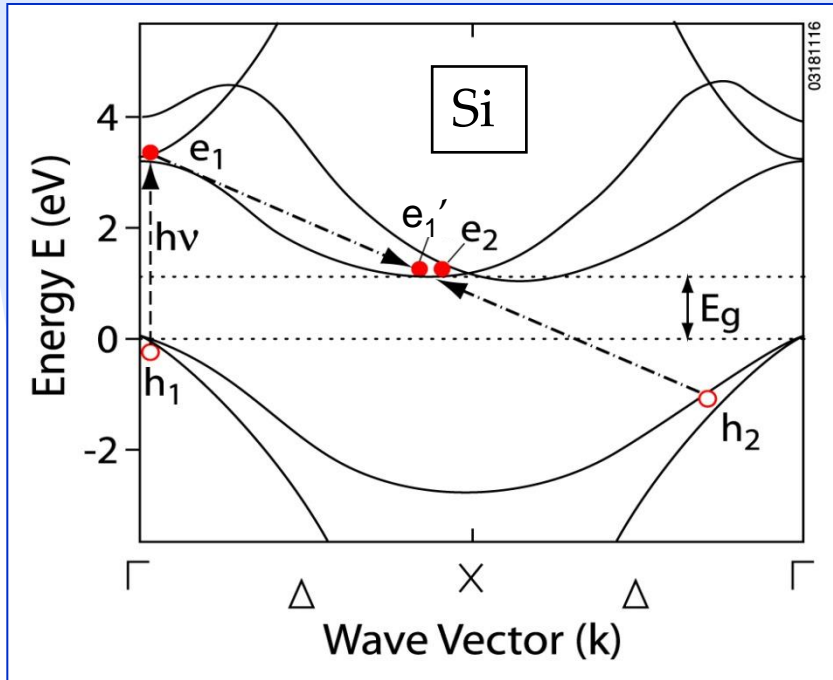
1 photon  $\rightarrow$   
1 hot electron

## 2. **Higher photocurrent:** carrier multiplication through impact ionization (inverse Auger process)

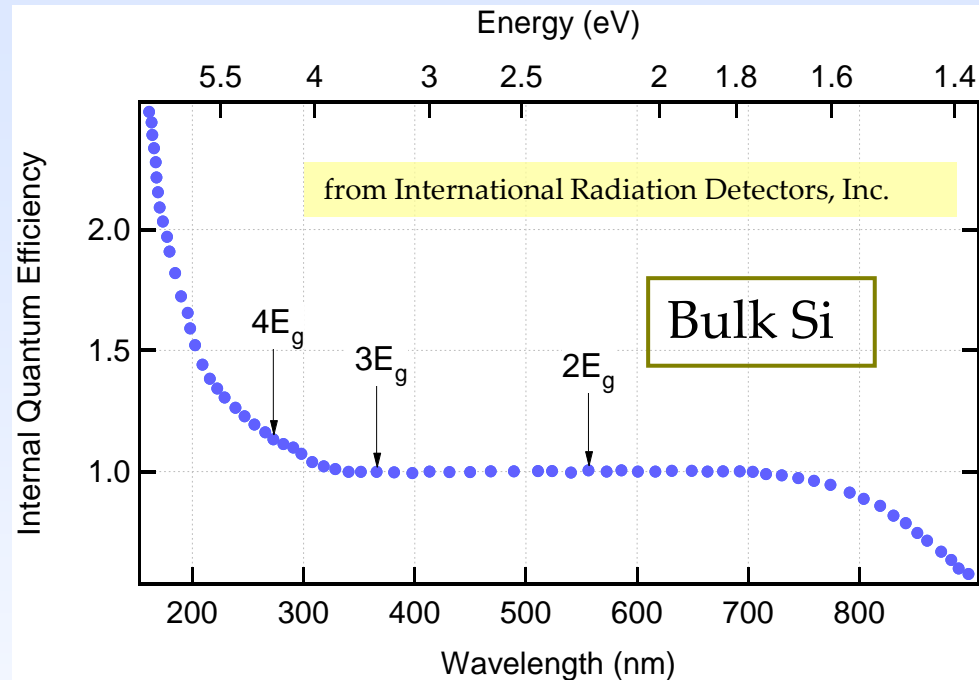


1 photon  $\rightarrow$   
2 (or more)  
cooled  
electrons

# Impact ionization in bulk semiconductors



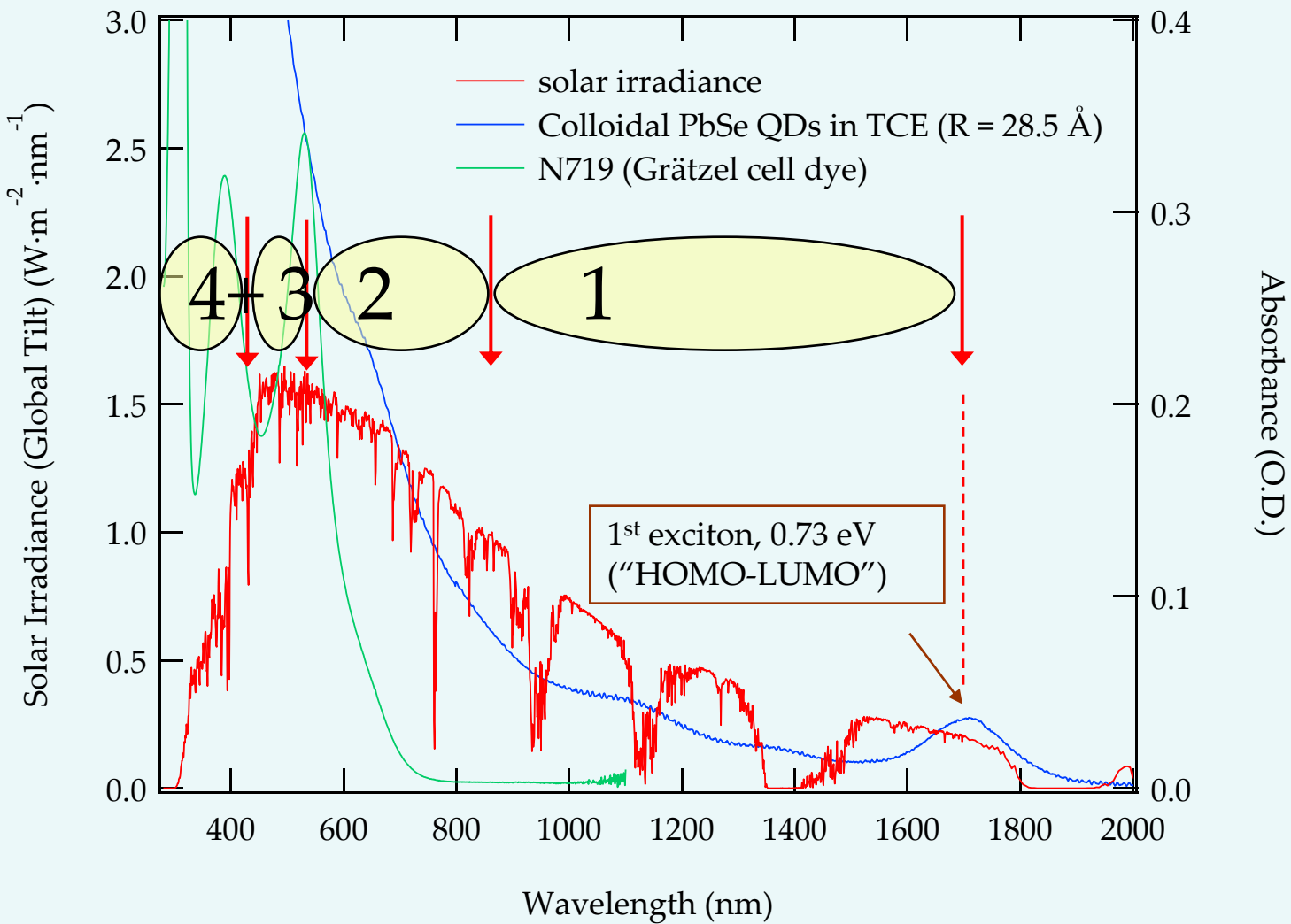
From Quiesser *et al.*, Appl. Phys. Lett. (1993).



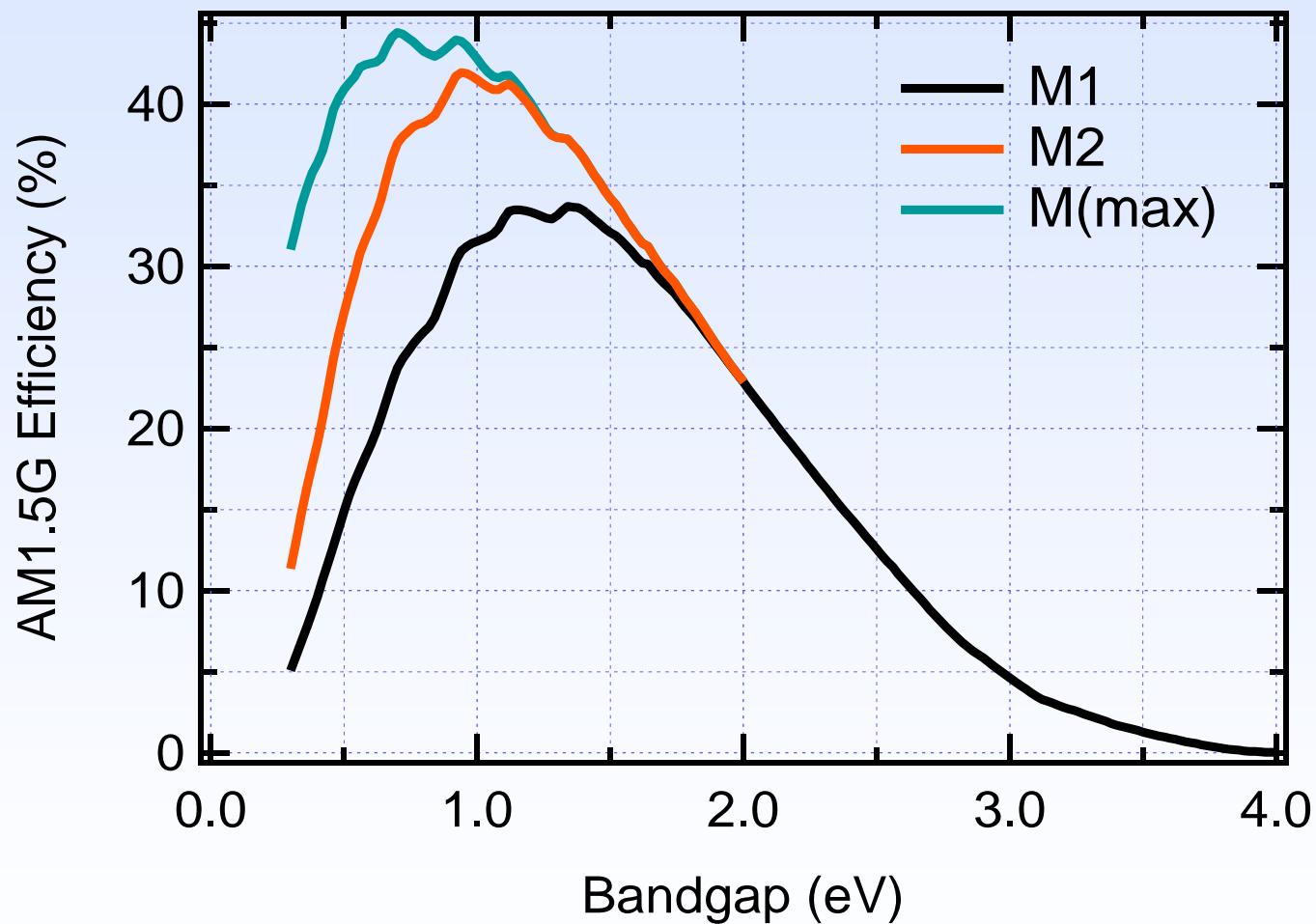
- Bulk Silicon ( $E_g \approx 1.1$  eV) exhibits an I.I. QY of just 1.2  $e^-h^+$  pairs per photon absorbed at 4.5 eV ( $\lambda = 275$  nm,  $hc/\lambda > 4 E_g$ ).
- Electron-phonon scattering dominates over I. I. up to very high photon energies.
- Nanocrystals exhibit a *reduced* momentum conservation requirement (NC surface can supply or absorb momentum during scattering processes).

# Enhancing conversion efficiency using NCs & MEG

## Matching absorption to solar irradiance spectrum



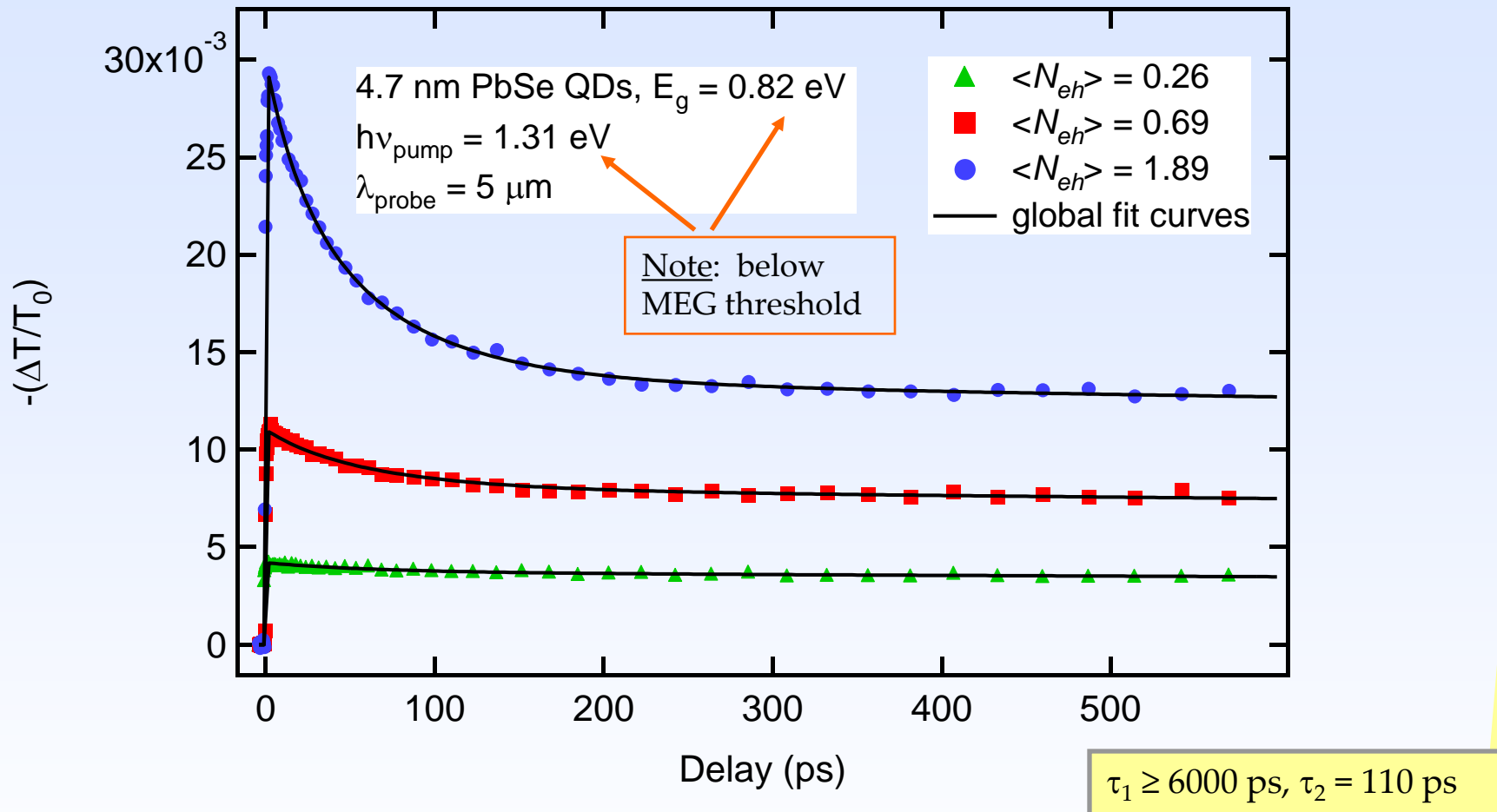
# MEG-active solar cells – efficiency limitations



from Mark Hanna, NREL



# Signature of multiple excitons: Auger recombination



Global fit for three intensities; excitation *below* the MEG threshold energy:

$$\Delta\alpha(t) \propto A_1 \exp(-t/\tau_1) + A_2 \exp(-t/\tau_2) + A_3 \exp(-t/\tau_3) + \dots$$

where the pre-exponential factors  $A_i = \sum_{m=i}^{\infty} P(m)$



# How efficiently is excess energy converted to excitons?

